

BRUKER NANO ANALYTICS

# Microanalysis Of Battery Materials

Bruker KOREA  
Application Team  
[Sungji.choi@bruker.com](mailto:Sungji.choi@bruker.com)

EDS  
XFlash®  
Technology

## Presenters

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### Sungji Choi

- Application specialist
- **EDS / EBSD / FlatQUAD / Micro-XRF / WDS**
- Bruker Nano Analytics, Korea

# How to get the most information – use FlatQUAD for better detection

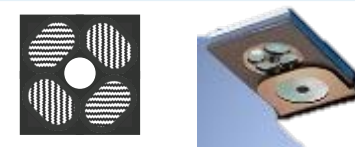
XFlash® 760



XFlash® FlatQUAD



SDD geometry



HV

Up to 30 kV

up to 20 kV

WD (min)

~ 4 mm

~ 8 mm

Window

optional

multiple

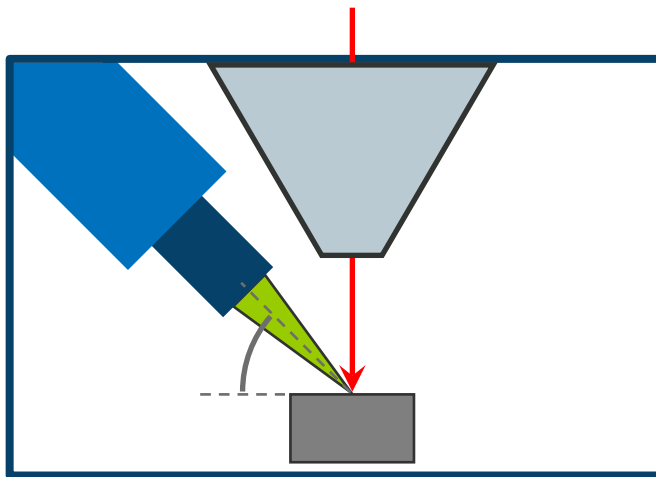
Solid angle (up to)

0.1 sr

1.1 sr

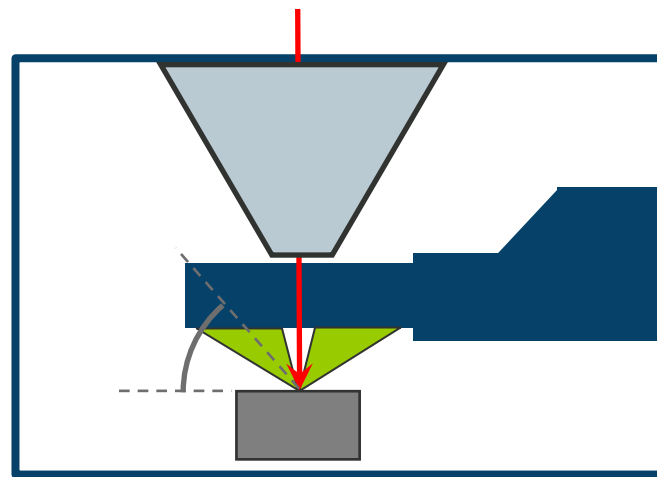
## How to get the most information – use FlatQUAD for better detection

Conventional detector  
60 mm<sup>2</sup> EDS detector  
@WD= 10mm



take off angle=35°  
solid angle=0.043 sr

FlatQUAD detector  
60 mm<sup>2</sup> (4x15mm<sup>2</sup>)  
@WD=10mm

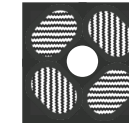
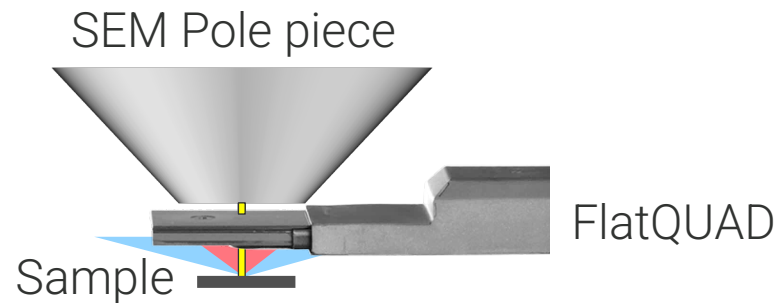


take off angle=60-70°  
solid angle = 1.1 sr

→ **Better view of sample topography**  
→ **x15-30 more X-ray signal:  
less measurement time needed**

# Bruker XFlash® FlatQUAD detector

## Features and advantages

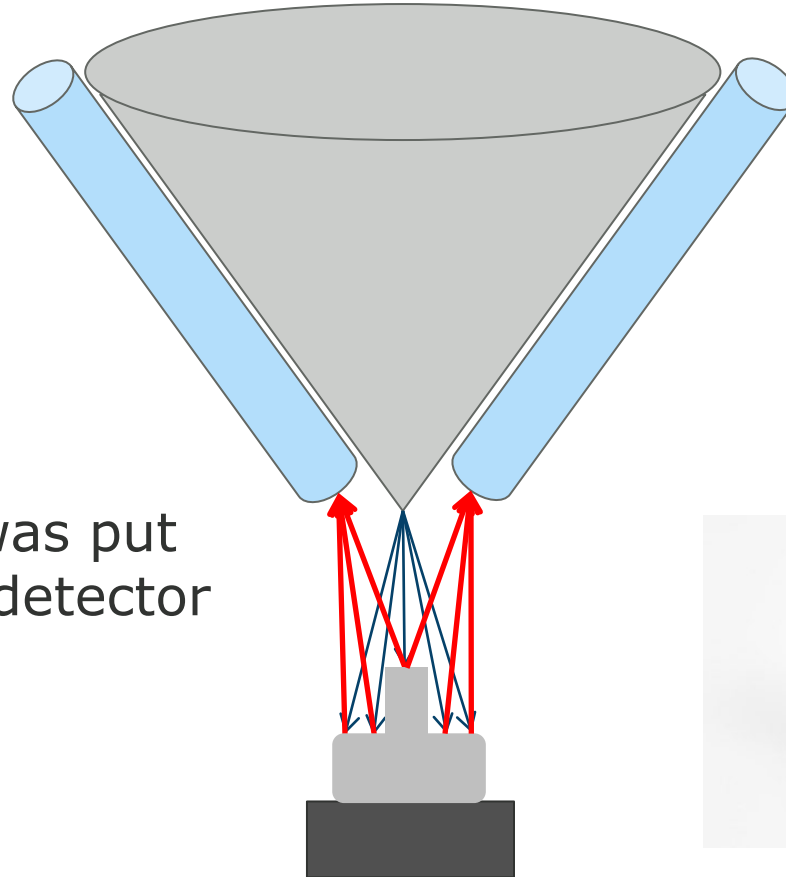


- Annular 4-segment (4x) SDD geometry, central ap.
- Side entry EDS (STEM/BSE like)
- Large solid angle of 1.1 sr
- High take-off angle (~60°)
- Optimal signal collection geometry
- High sensitivity at very low probe currents ~few pA
- Minimize sample charging/damage/C-deposition at low PC
- High vacuum conditions EDS – high resolution
- Low vacuum capability
- Moderate probe currents for high-speed EDS mapping
- Low x-ray yield samples: Low PC – High resolution
- Nanoparticles, Thin lamellae, beam sensitive materials

# Shadow effect

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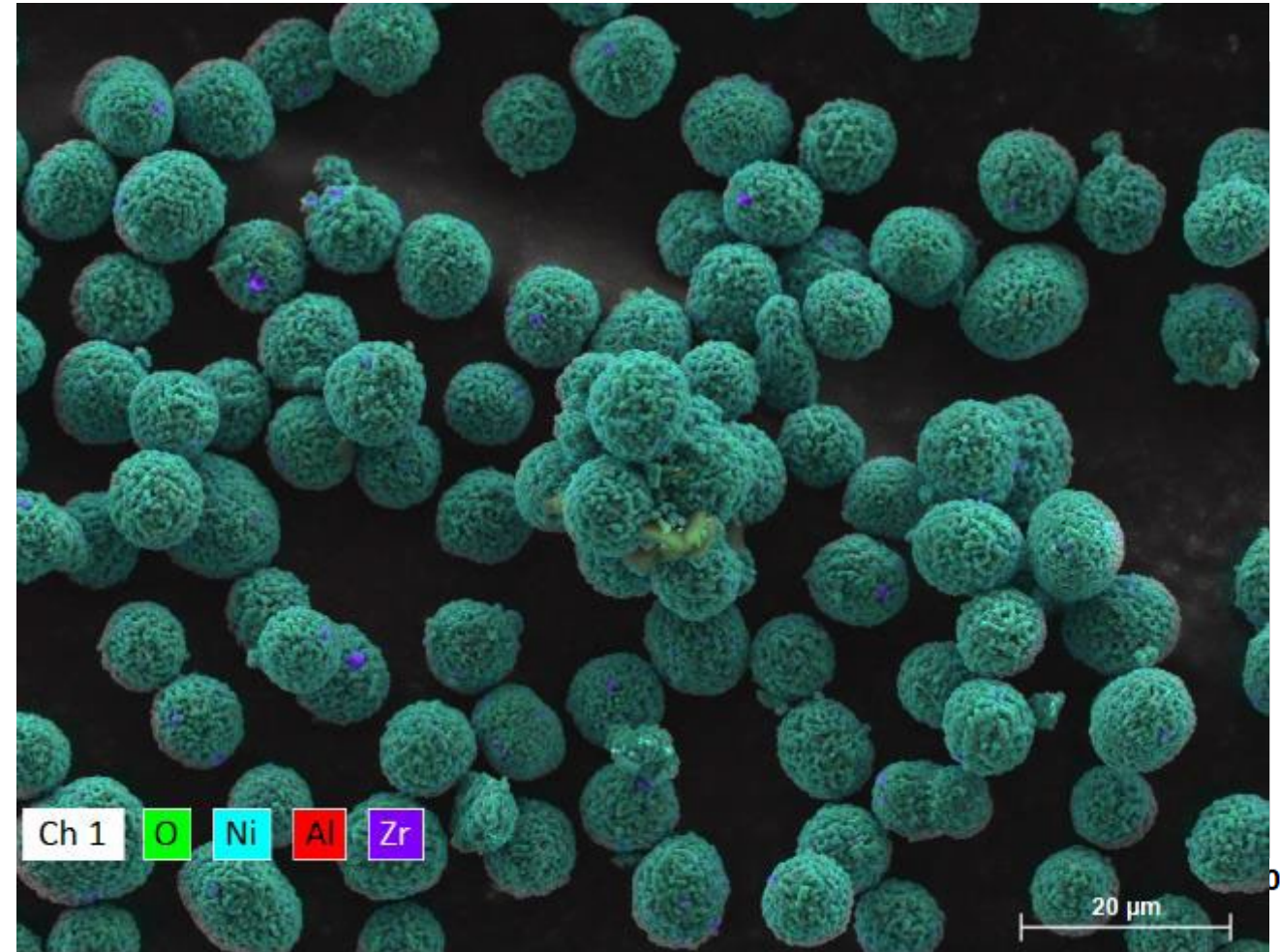
SEM-EDS system was put on a just one EDS detector at common



If your samples having a **roughness at surface**,  
Easy to get a shadow effect **by one way detection**

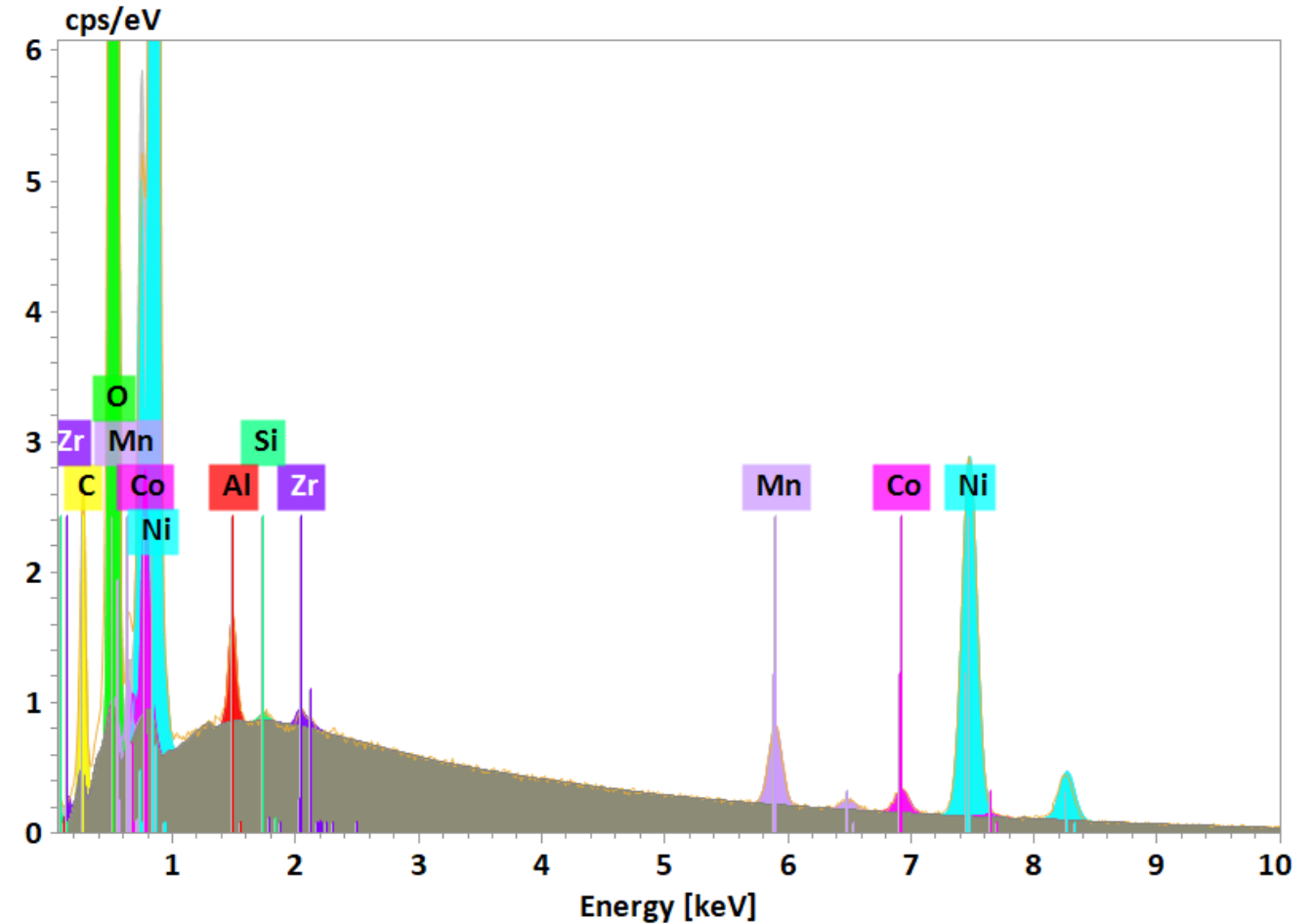
## Pre-screening of NCM particles

- Electron microscopy: SE imaging gives morphological information.
- Flatquad EDS detector allows for very fast mapping of spherical particles without shadowing effect (full particle is mapped)
- High sensitivity allows detection of contaminants in short time.
- No low vacuum, no inert gas transfer and no sample coating needed
- Sample: NCM particles (raw material) loosely distributed on sticky carbon pad



# Pre-screening of NCM particles

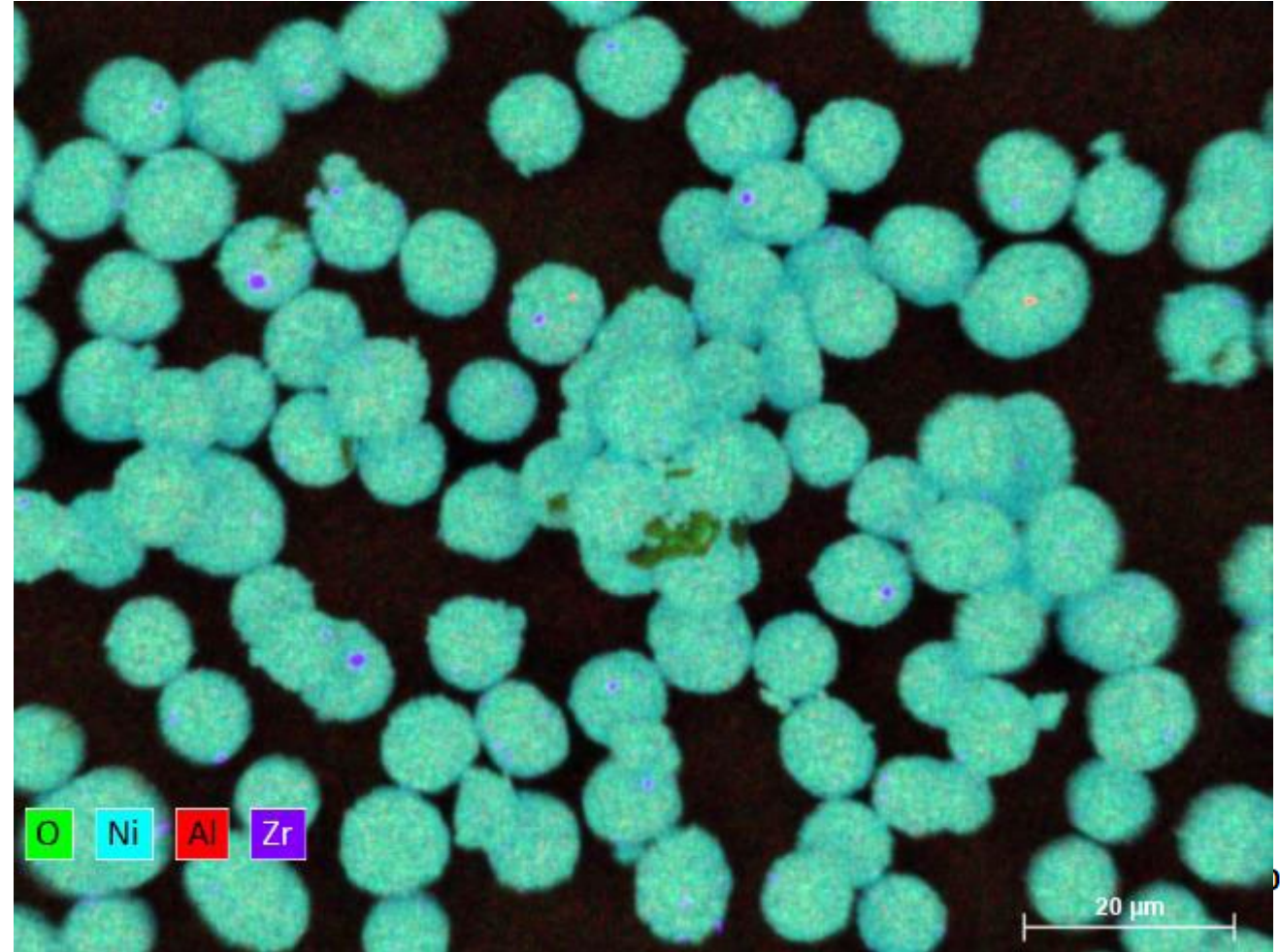
- Sum spectrum: elements are identified
- Individual element maps:
  - C: sample substrate
  - Ni, Co, Mn: NCM main components
  - O: inhomogeneity of oxide material, oxidation, contamination?
  - Al: sintering agent or dopant?
  - Zr: sintering agent or dopant?



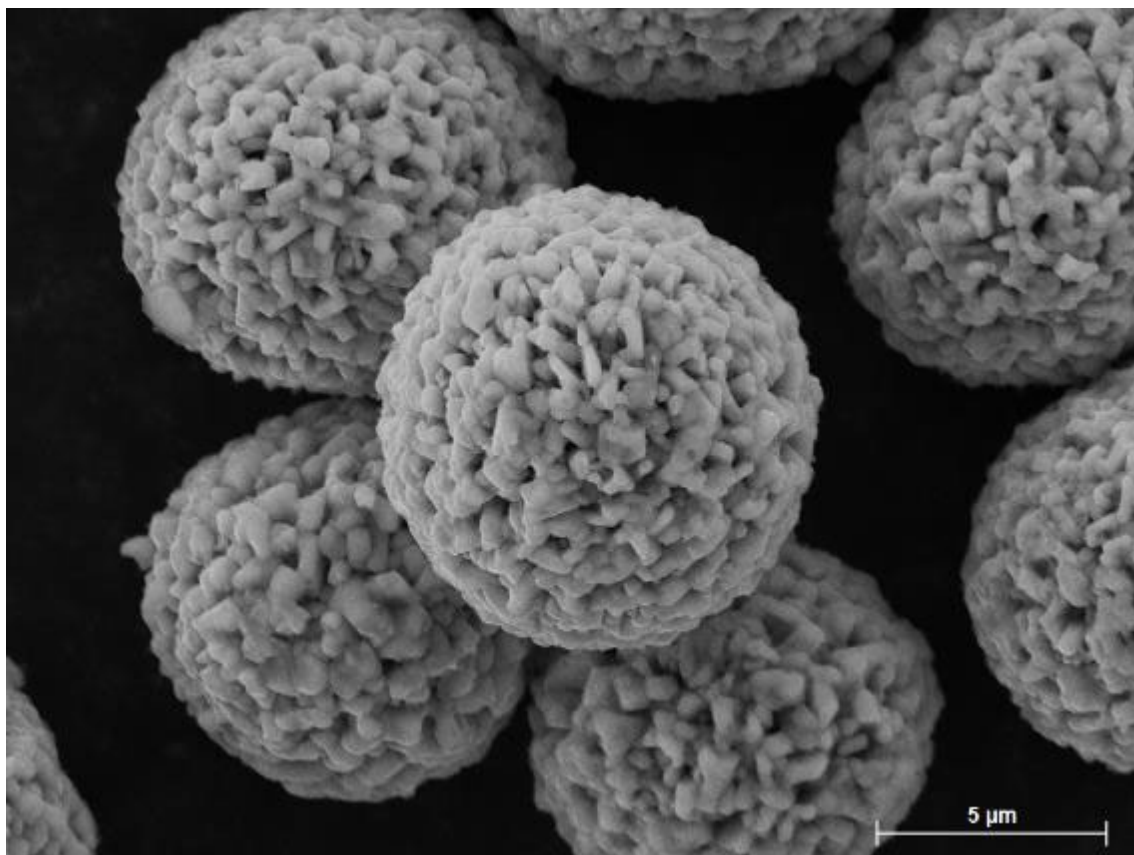


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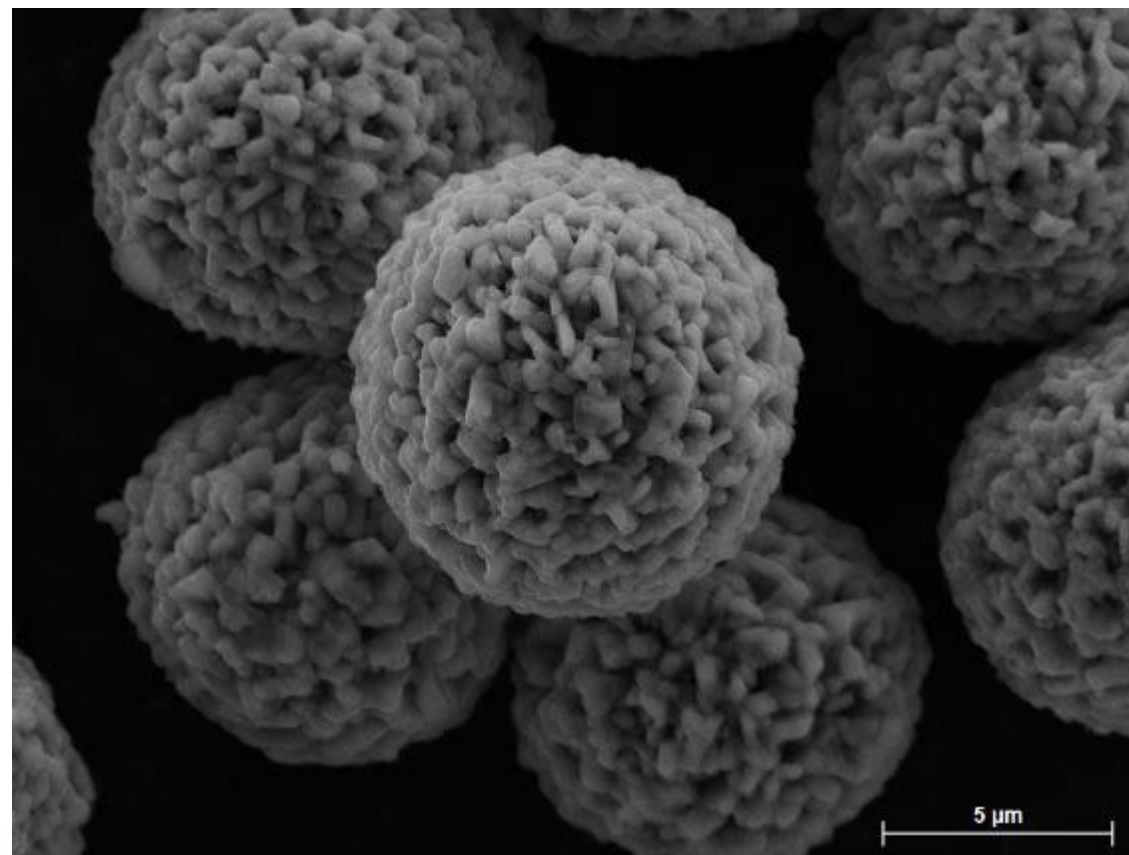


# Pre-screening of NCM particles



Conventional EDS

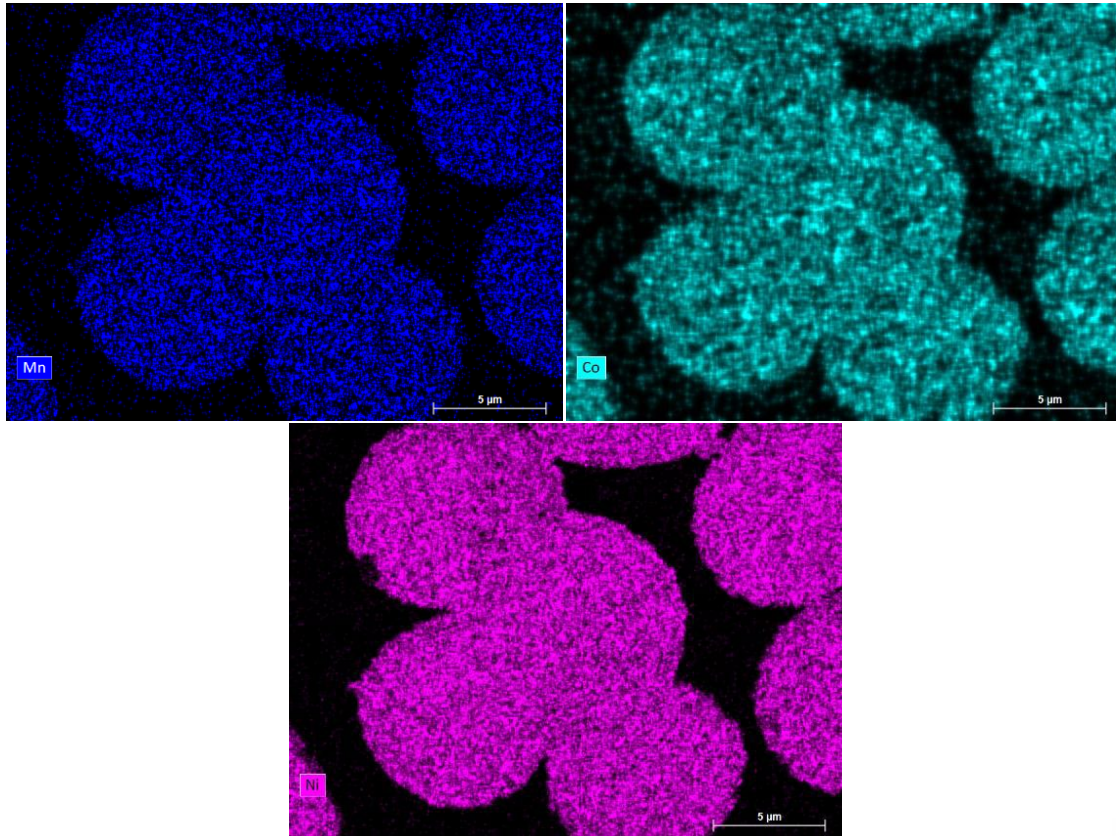
12 kV / 510pA



XFlash® FlatQUAD

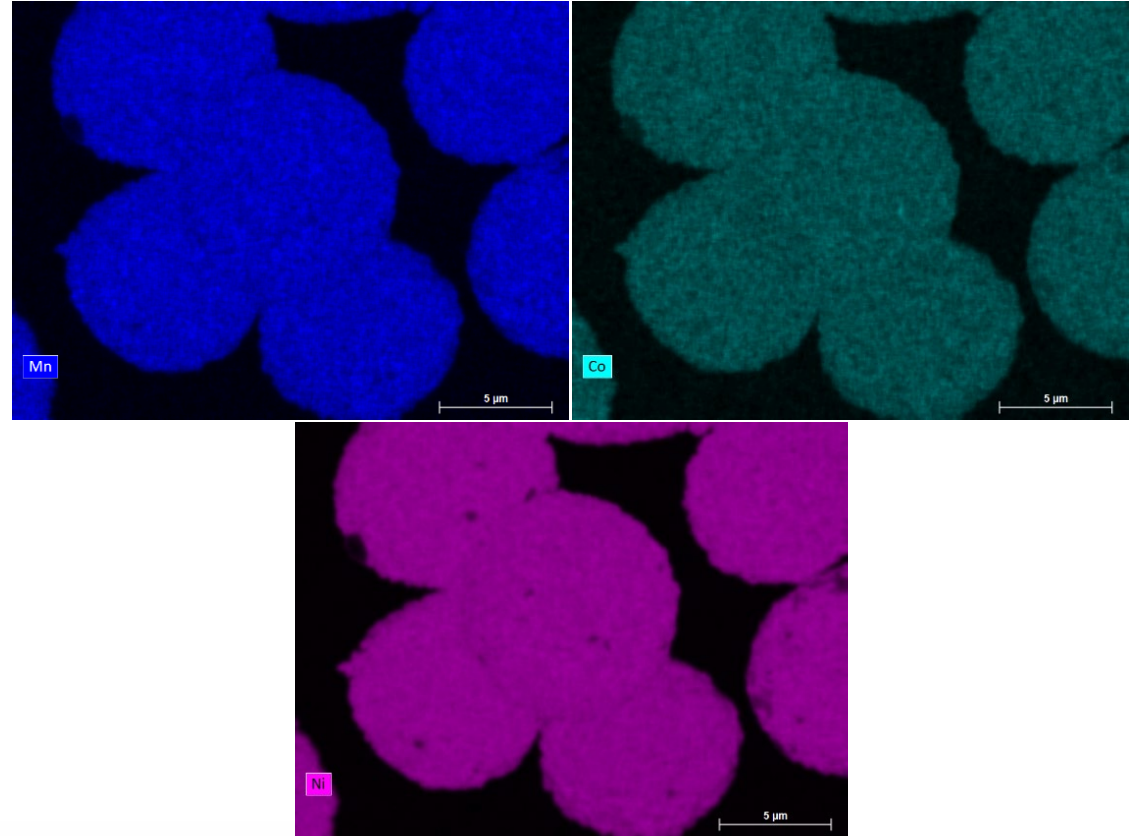
12 kV / 510pA

# Pre-screening of NCM particles



Conventional EDS

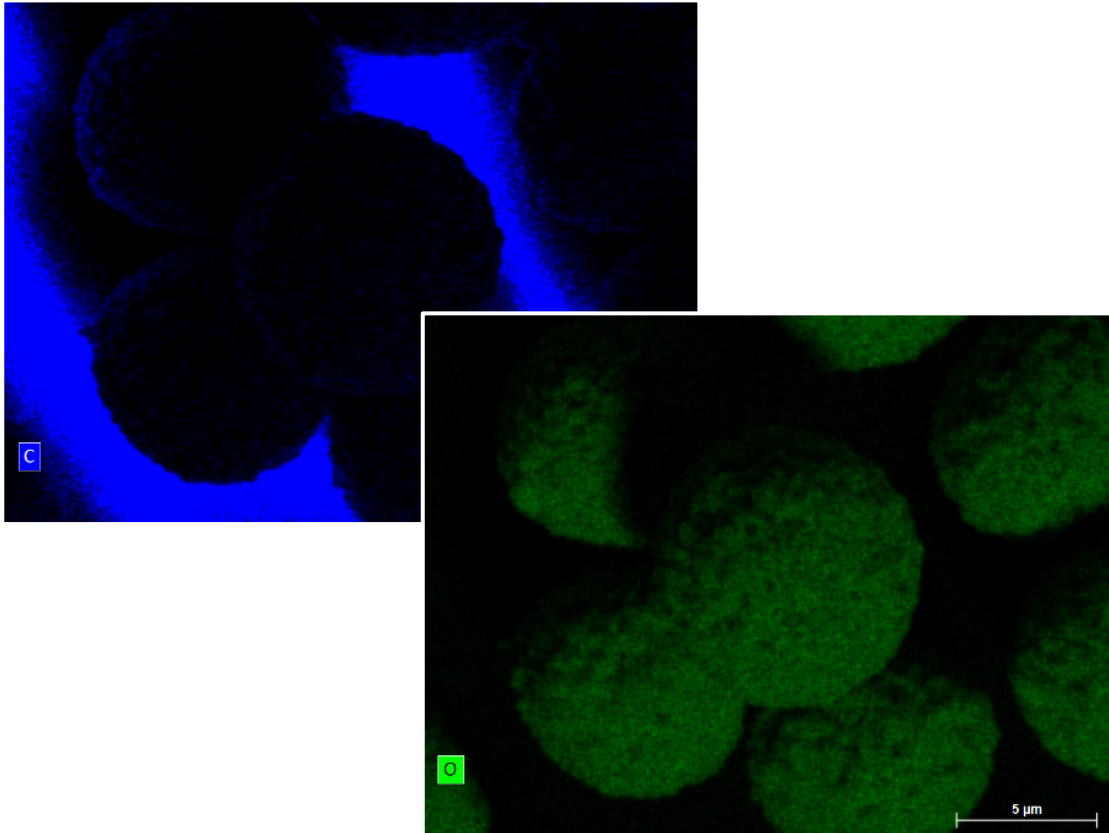
12 kV / 510pA / 600s / 7,190 cps



XFlash® FlatQUAD

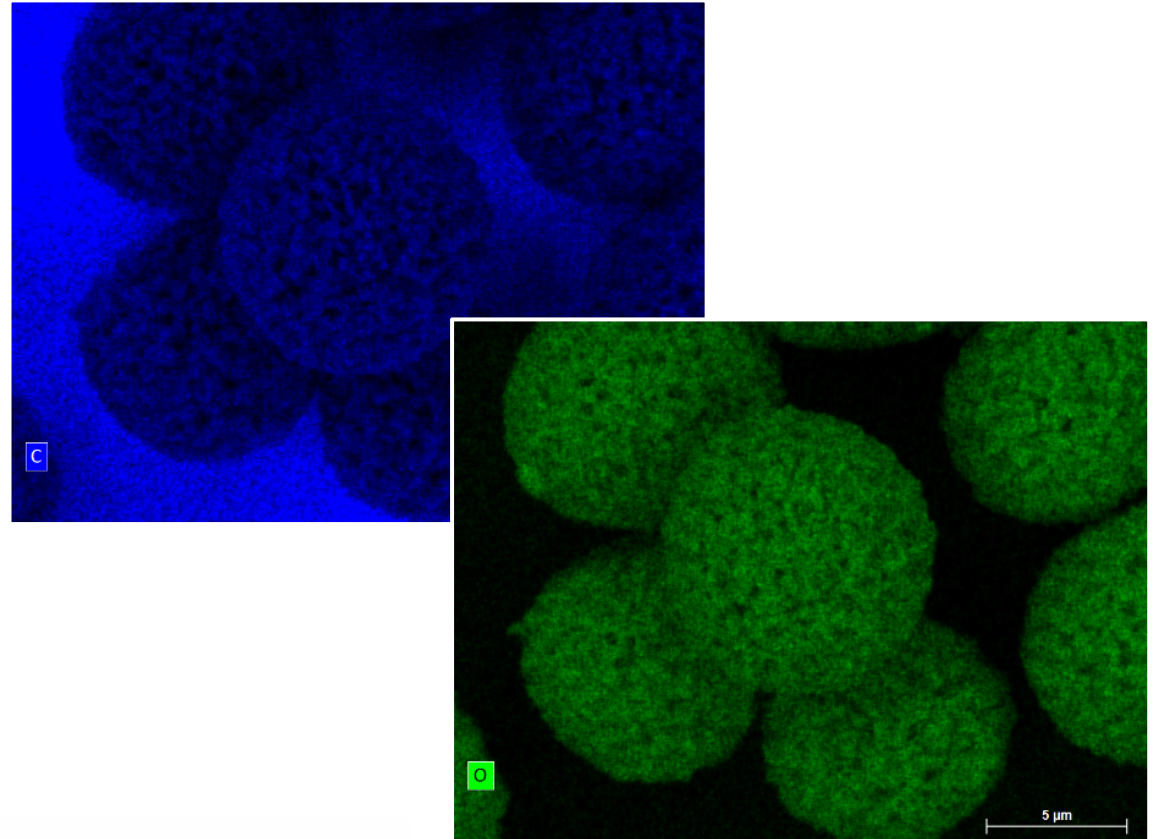
12 kV / 510pA / 600s / 133,900 cps

# Pre-screening of NCM particles



Conventional EDS

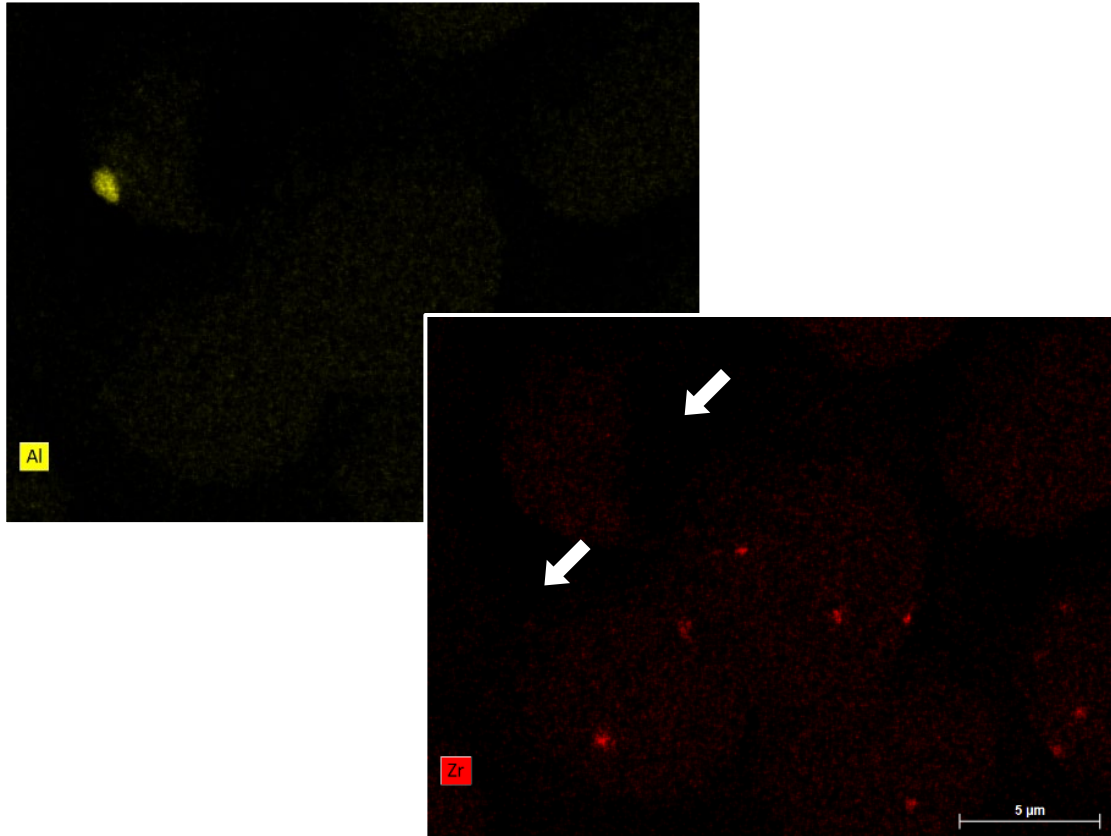
12 kV / 510pA / 600s / 7,190 cps



XFlash® FlatQUAD

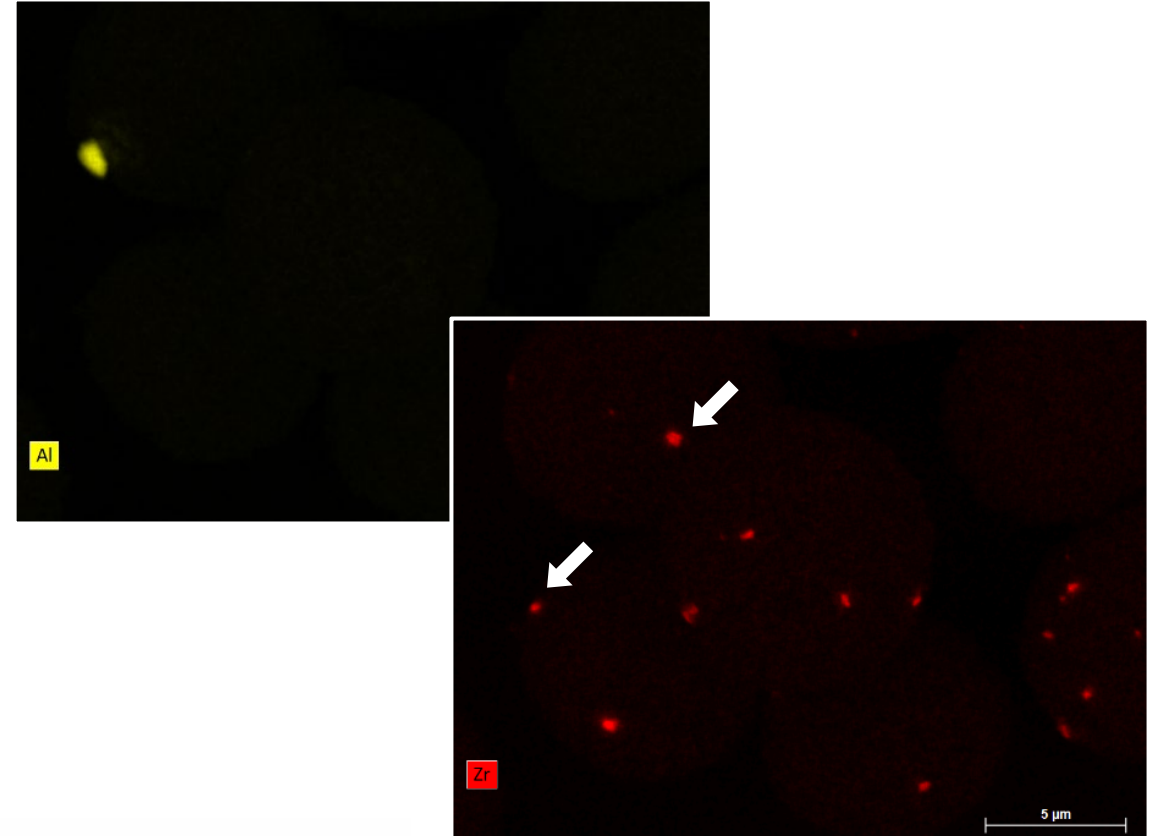
12 kV / 510pA / 600s / 133,900 cps

# Pre-screening of NCM particles



Conventional EDS

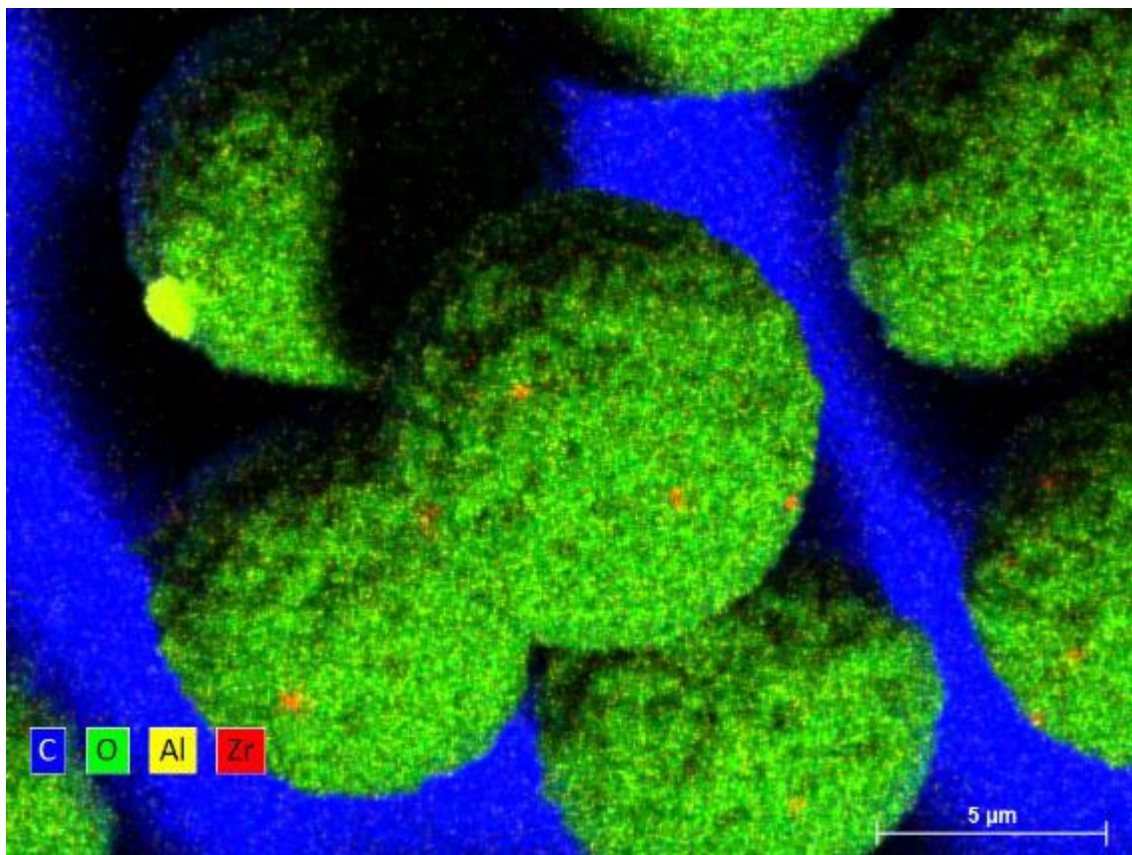
12 kV / 510pA / 600s / 7,190 cps



XFlash® FlatQUAD

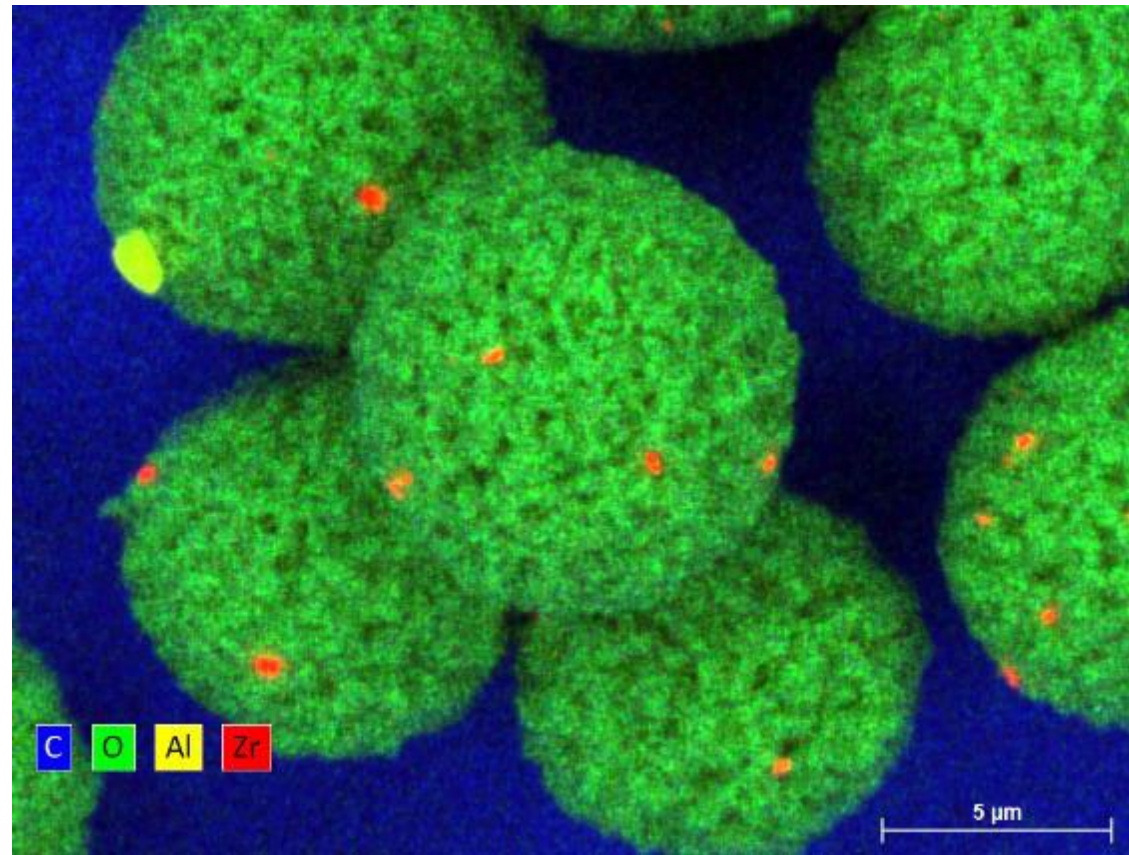
12 kV / 510pA / 600s / 133,900 cps

# Pre-screening of NCM particles



Conventional EDS

12 kV / 510pA / 600s / 7,190 cps



XFlash® FlatQUAD

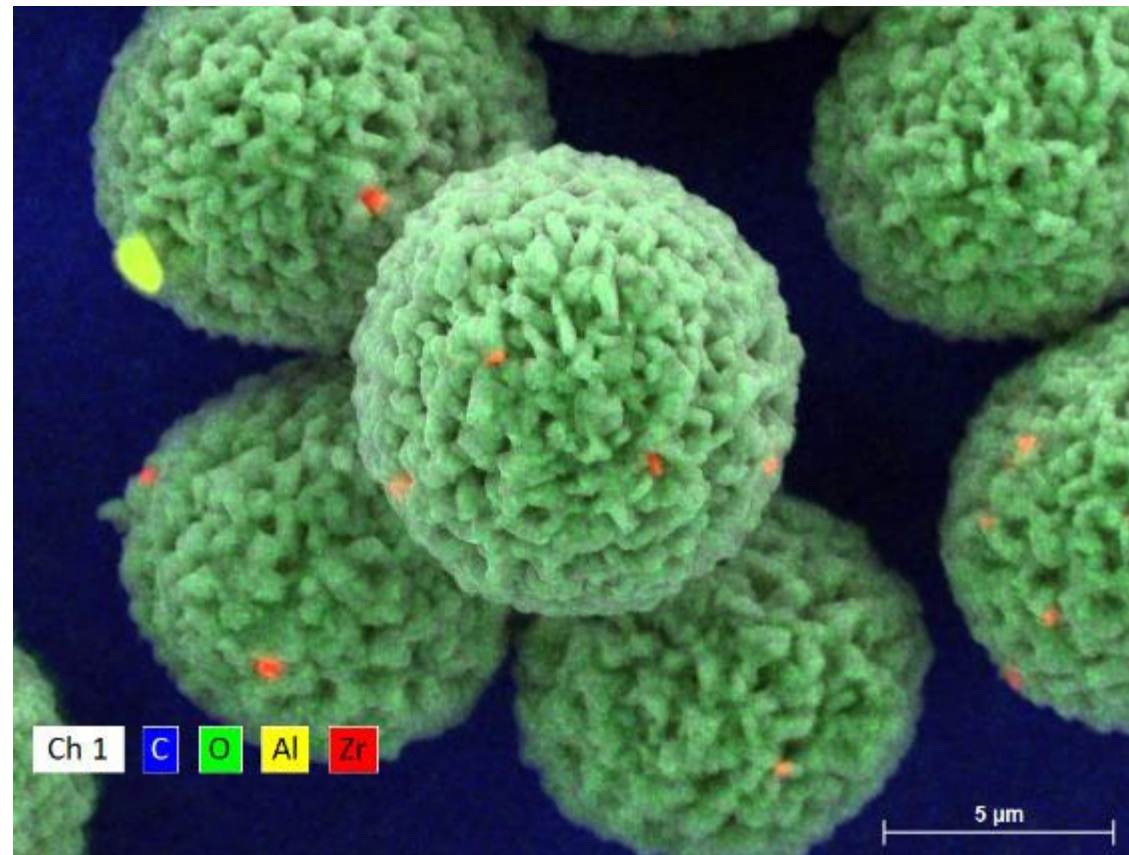
12 kV / 510pA / 600s / 133,900 cps

# Pre-screening of NCM particles



Conventional EDS

12 kV / 510pA / 600s / 7,190 cps

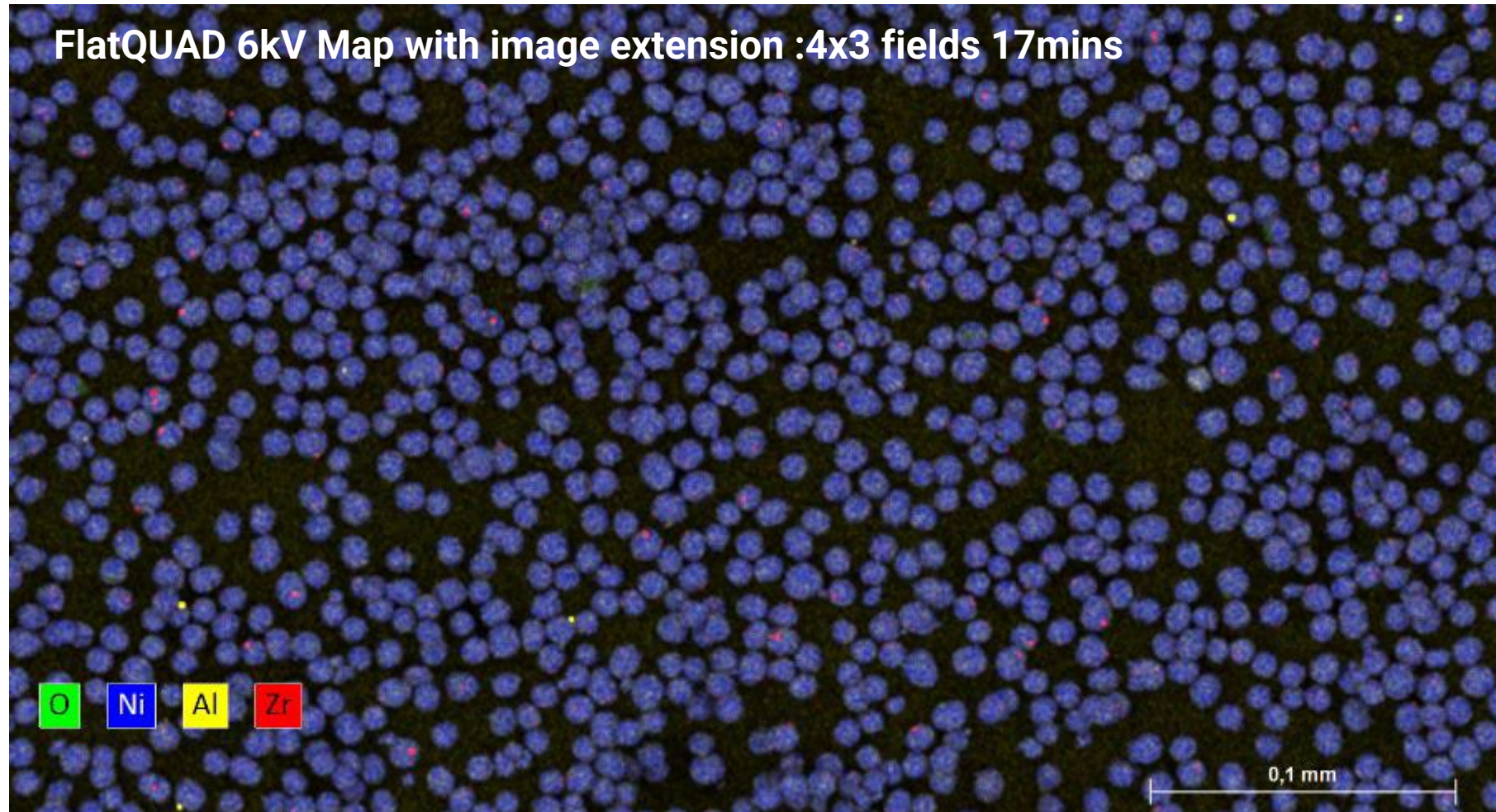


XFlash® FlatQUAD

12 kV / 510pA / 600s / 133,900 cps

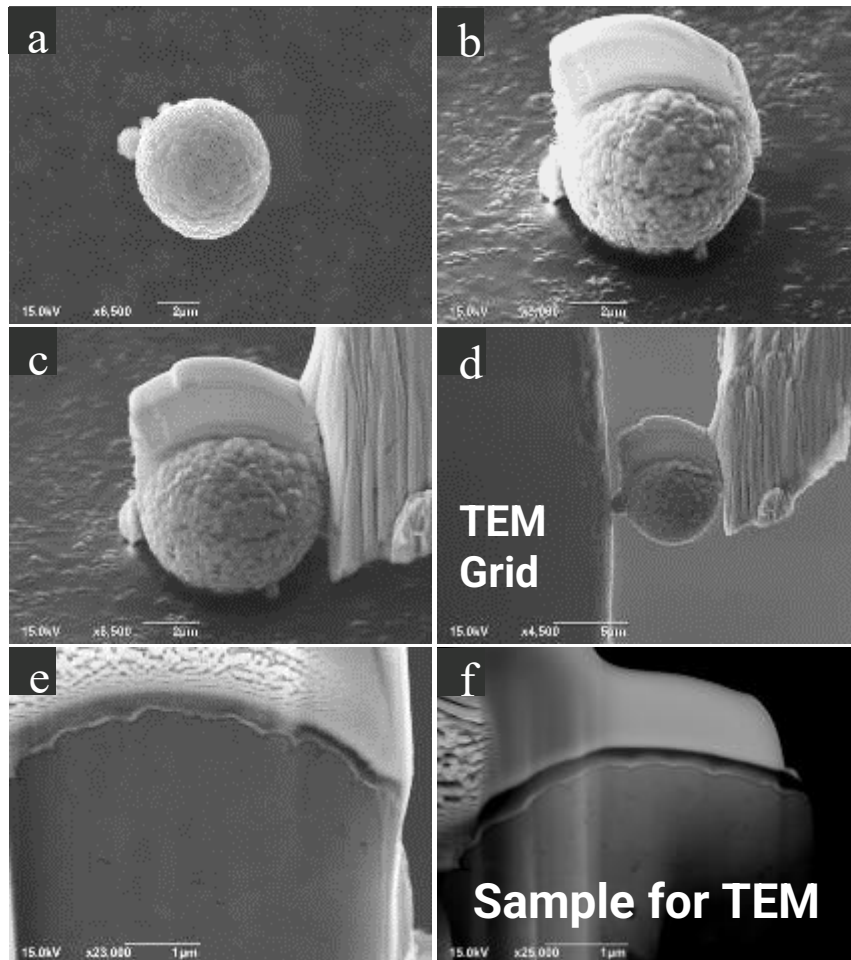
## Pre-screening of NCM particles: large area scans

- FlatQUAD makes fast element distribution maps possible: -> survey of large areas, particle screening with microscope stage automation:  
Use higher beam current to maximize count rate  
-> minimize analysis time



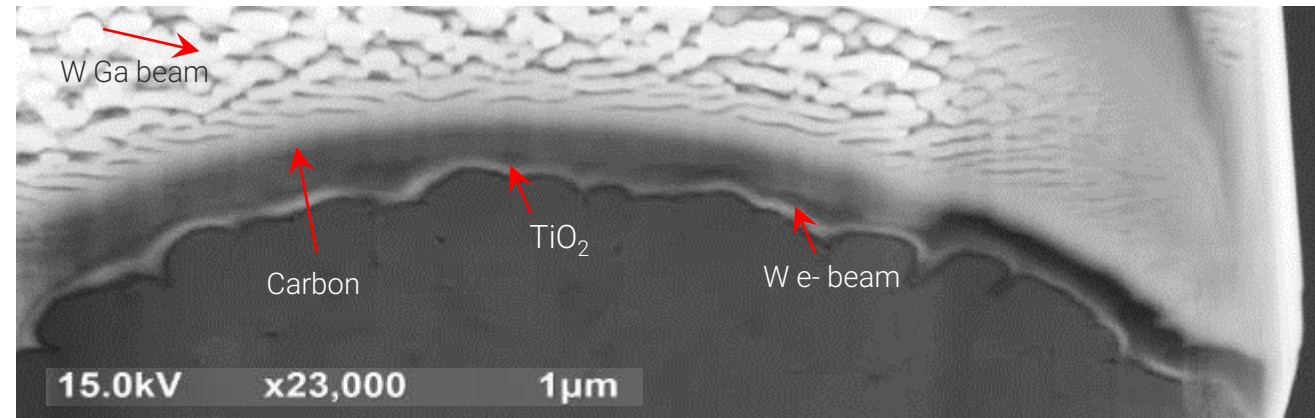


## ALD coated NCM particle - FIB lamella



**Motivation:** Ti-Coating to enhance capacity

**Challenge:** HAADF contrast can not distinguish between W protection layer and Ti coating → measure with EDS



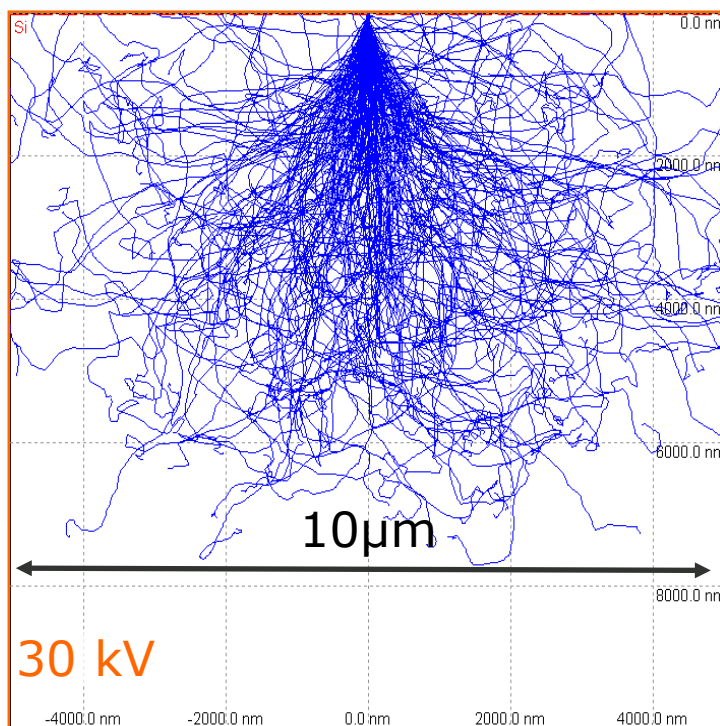
Watch on-demand joint webinar on on demand:

[Significance of STEM-EDXS Analysis in the Characterization of Rechargeable Battery Components](#)

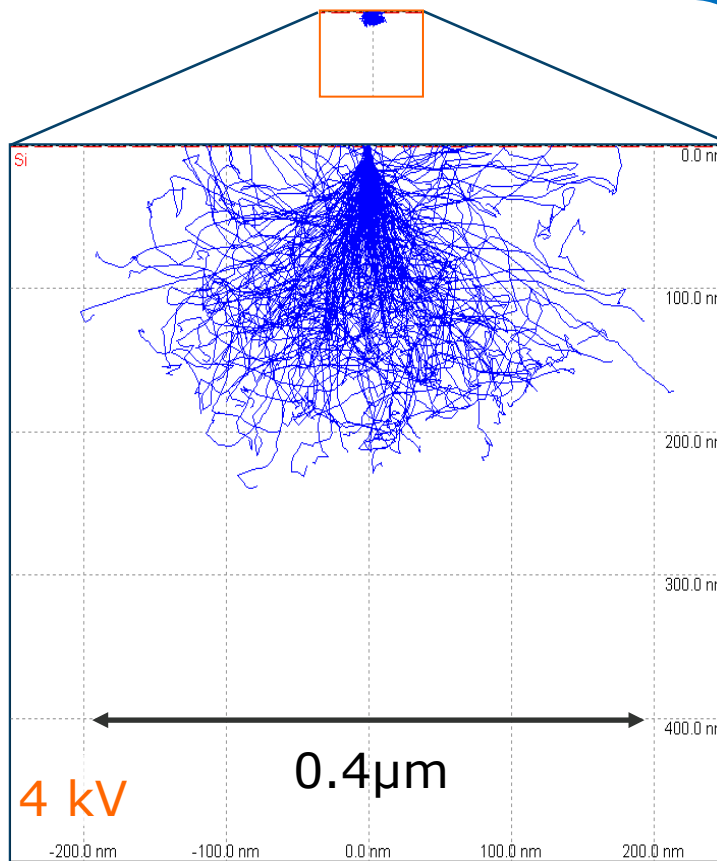
Data courtesy:  
M. Malaki, S. Ahmed, Philipps University  
Marburg, Germany

# Spatial resolution of X-rays analysis

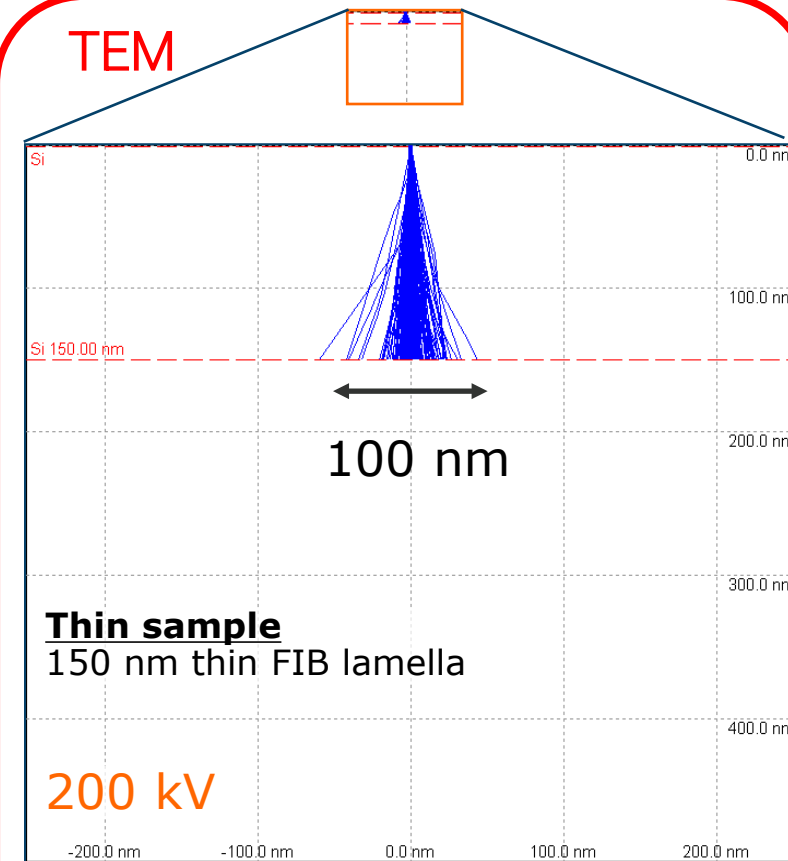
## SEM



Si bulk sample



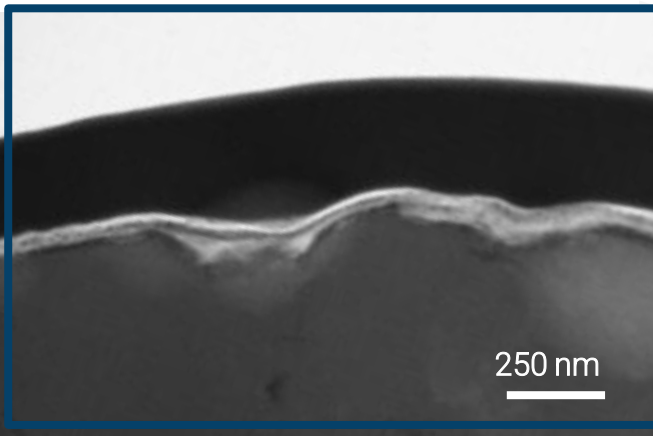
## TEM



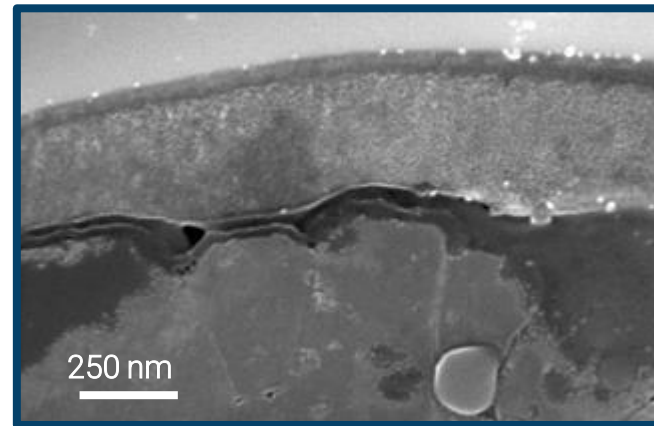
Thin sample  
150 nm thin FIB lamella

# ALD coated NCM particle sample: STEM/EDS-SEM/EDS comparison

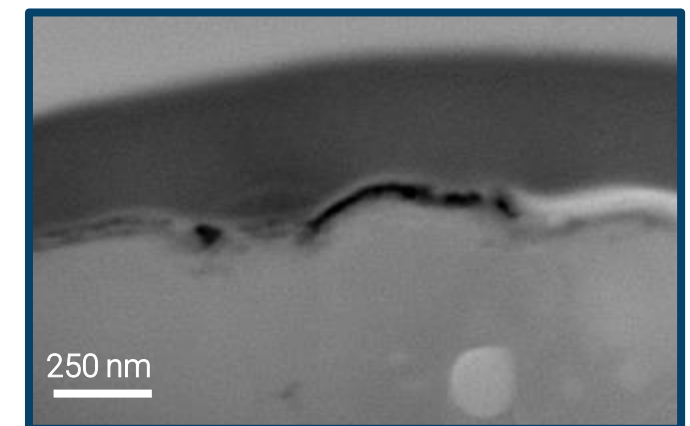
STEM 200kV  
HAADF image



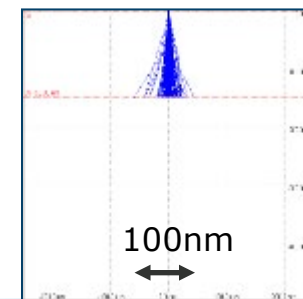
SEM 20kV  
In-lens image



SEM 20kV  
SE image with  
inserted FlatQUAD



Images taken under measurement conditions optimized for EDS analysis  
Image quality does not affect EDS resolution on this scale!

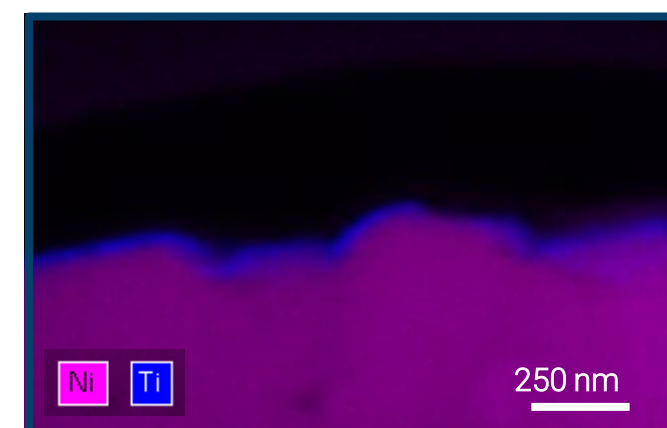
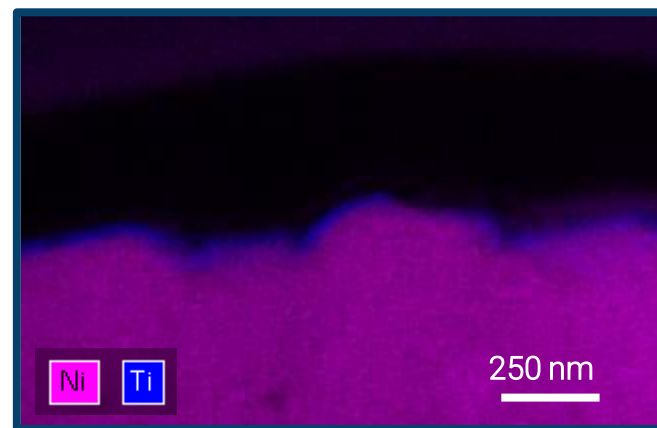
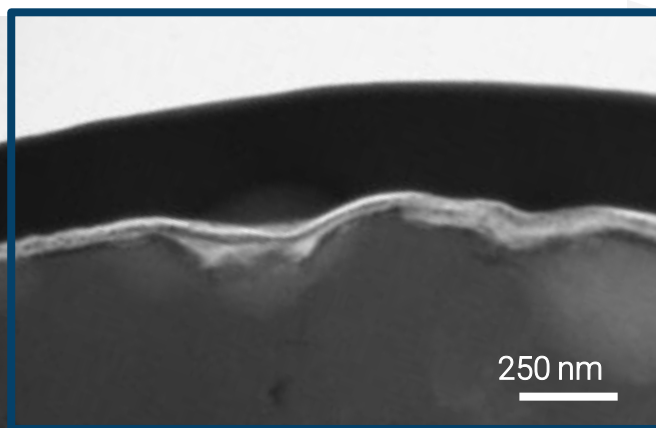


# ALD coated NCM particle sample: STEM/EDS-SEM/EDS comparison

STEM 200kV  
60 mm<sup>2</sup> EDS detector

SEM 20kV  
60 mm<sup>2</sup> EDS detector

SEM 20kV  
FlatQUAD detector



Total measurement time= 8 min  
Beam current= 0.2 nA  
Input count rate ~ 1,000 cps

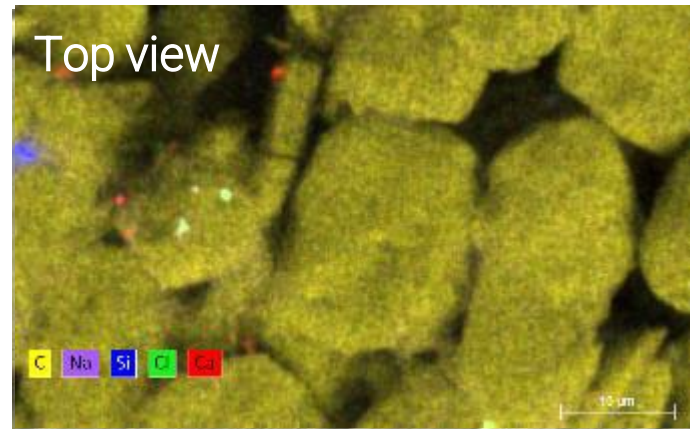
Total measurement time= 34 min  
Beam current=2 nA  
Input count rate ~ 30,000 cps

Total measurement time= 5 min  
Beam current= 2 nA  
Input count rate ~ 460,000 cps

# Ex-situ contamination analysis of anode/cathode material

Anode sample:

graphite on copper (not cycled)



Cathode sample:

LiPO4 on aluminum (not cycled)



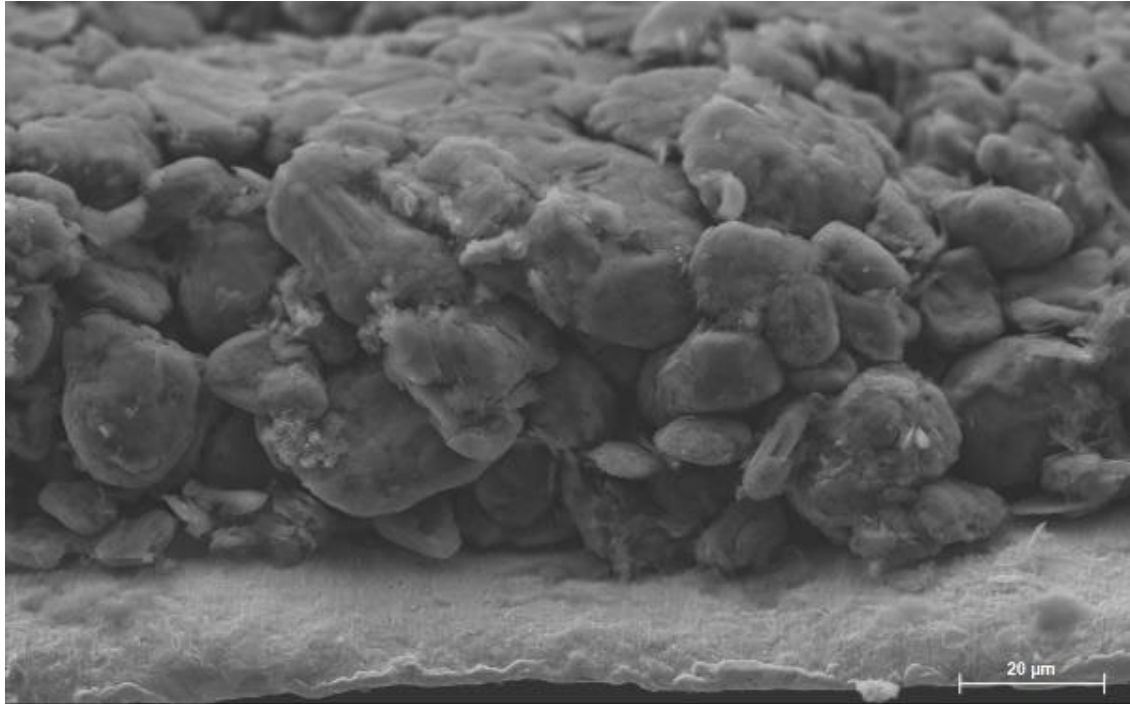
Join our joint webinar on 2<sup>nd</sup>  
November 2023!

[Elemental Mapping \(EDS\) for  
the Optimization of Battery  
Materials and Processes](#)

Register under:

<https://www.bruker.com>

## ANODE cross section – XFlash® 760 vs FlatQUAD

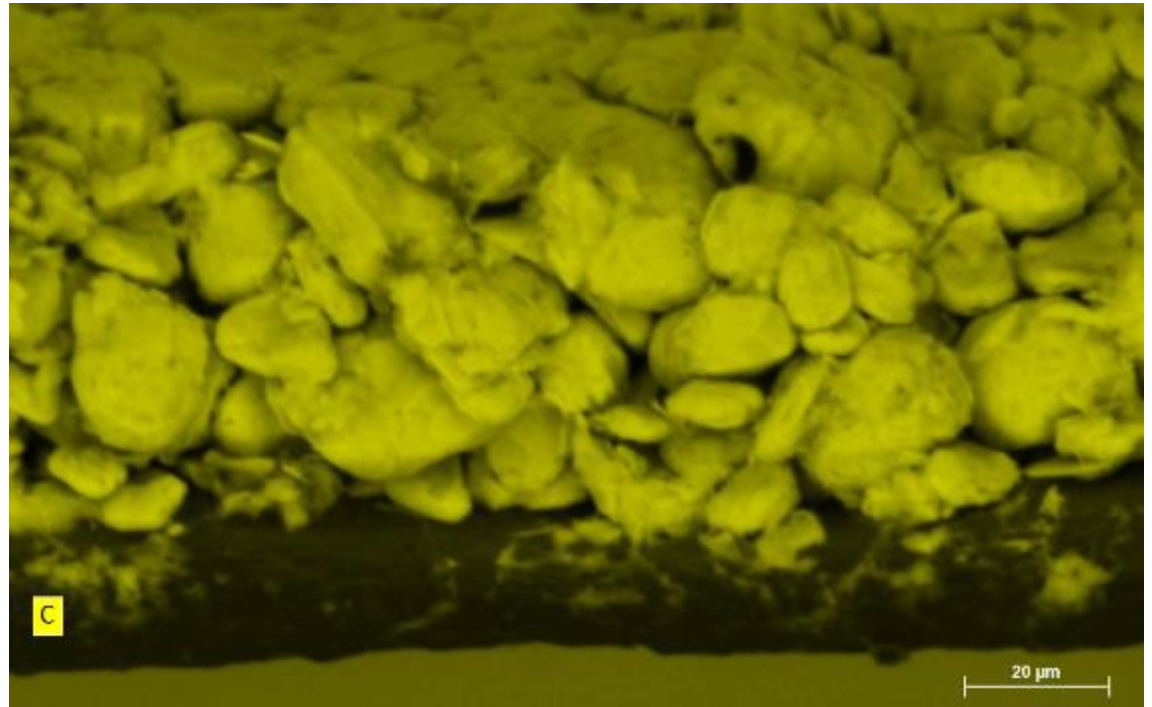
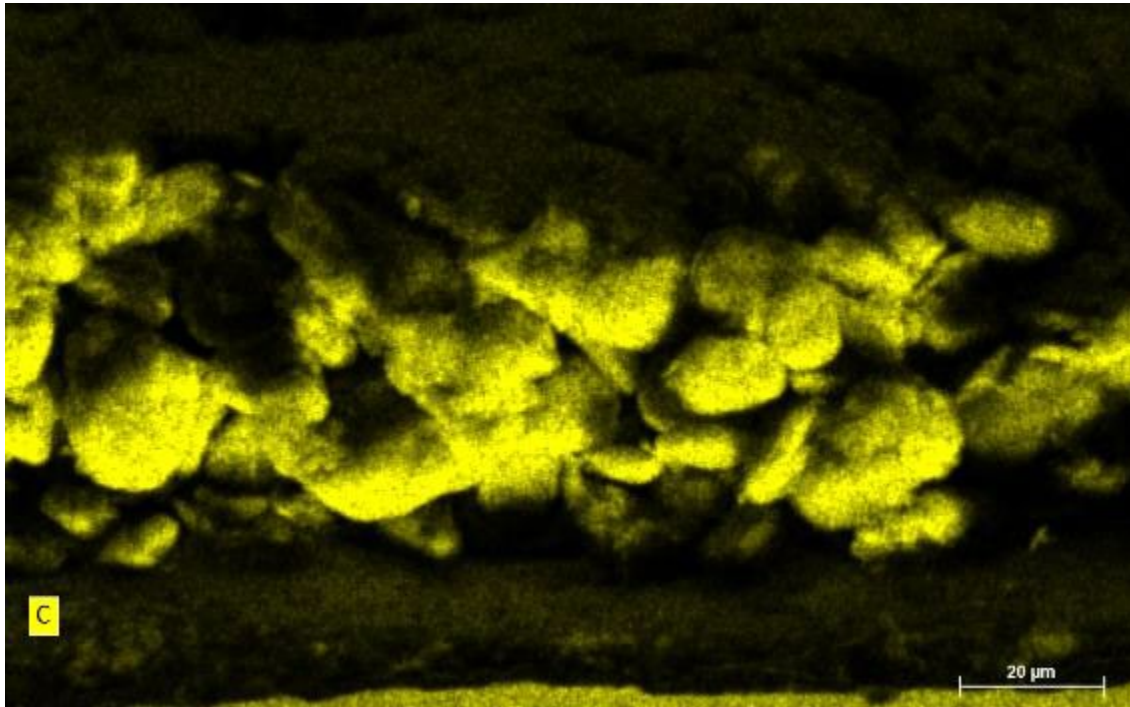


### Analysis parameters

Detector	XFlash® 760	XFlash® FlatQUAD
High voltage	12 kV	12 kV
Beam current	1.2 nA	1.2 nA
Mapping time	30 min	7 min
Input count rate (ICR)	19,500 cps	667,000 cps

# ANODE cross section – XFlash® 760 vs FlatQUAD

## Shadowed areas



XFlash® 760

XFlash® 760

12 kV / 1.2 nA / 30m / 19,500 cps

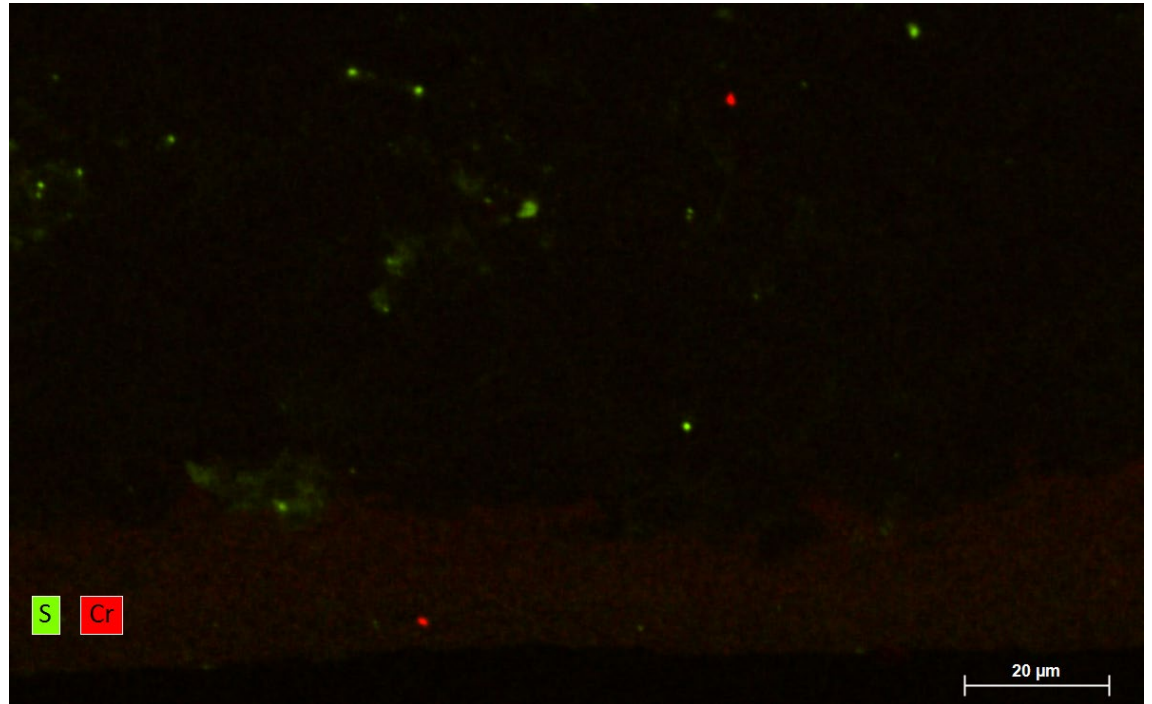
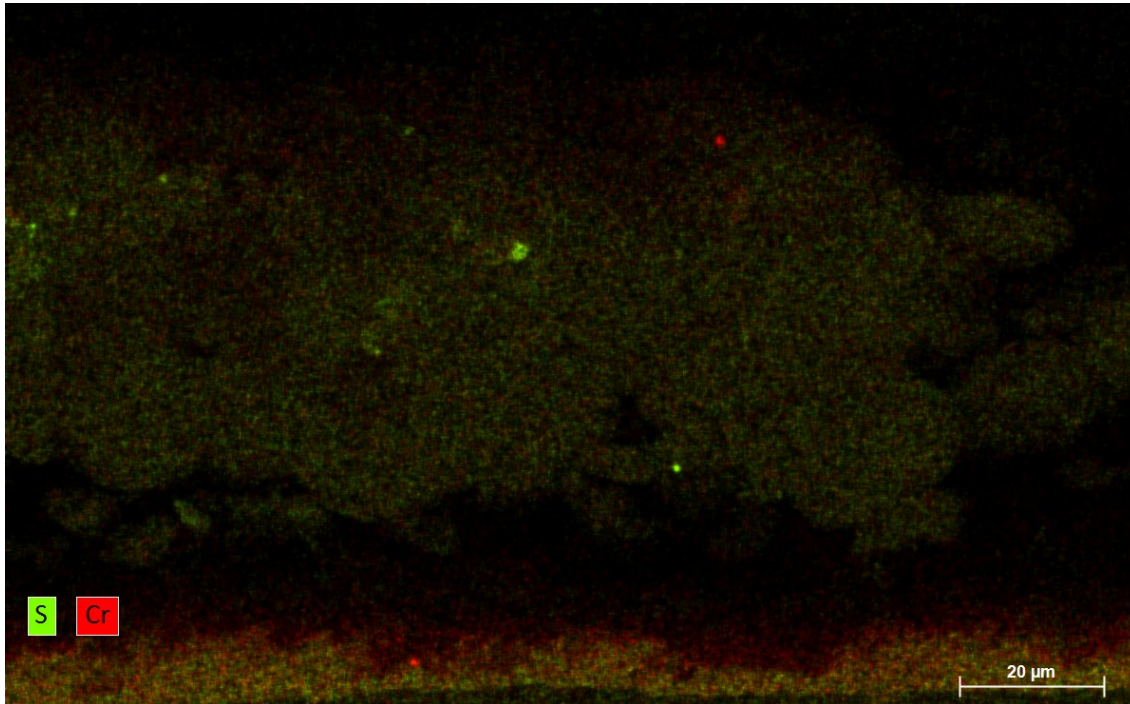


XFlash® FlatQUAD

XFlash® FlatQUAD

12 kV / 1.2 nA / 7m / 667,400 cps

# ANODE cross section – XFlash® 760 vs FlatQUAD: Finding “hiding elements”: S, Cr



XFlash® 760

Noisier maps,  
Shadowed areas

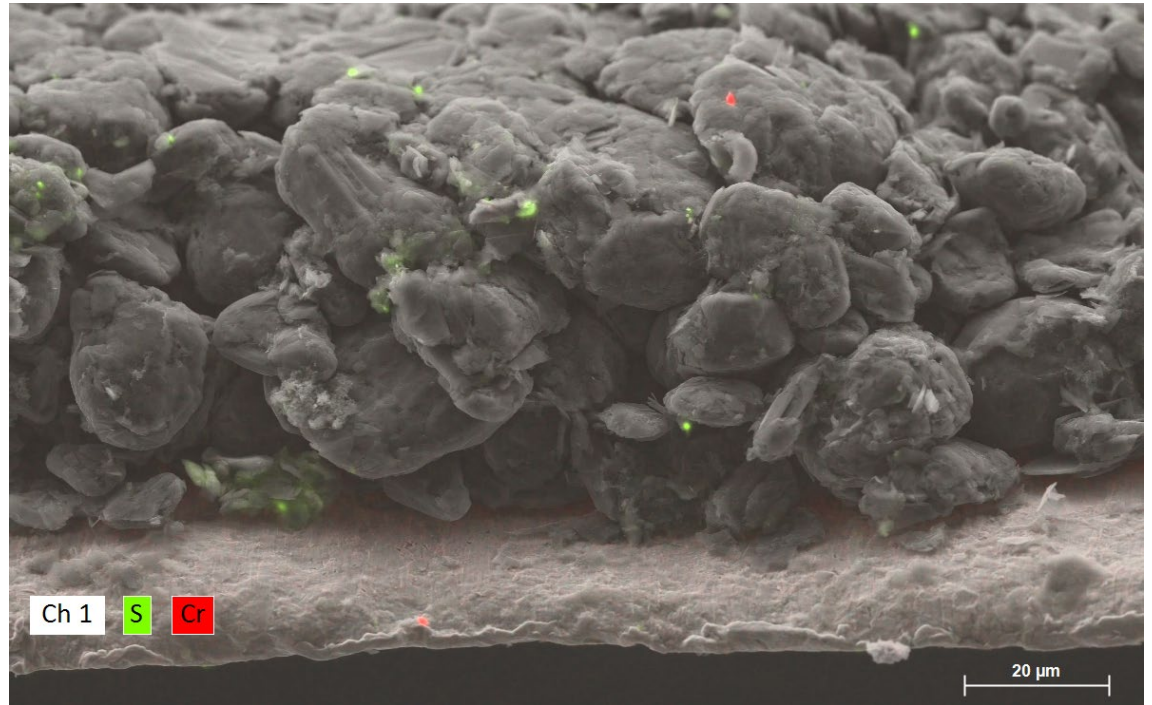
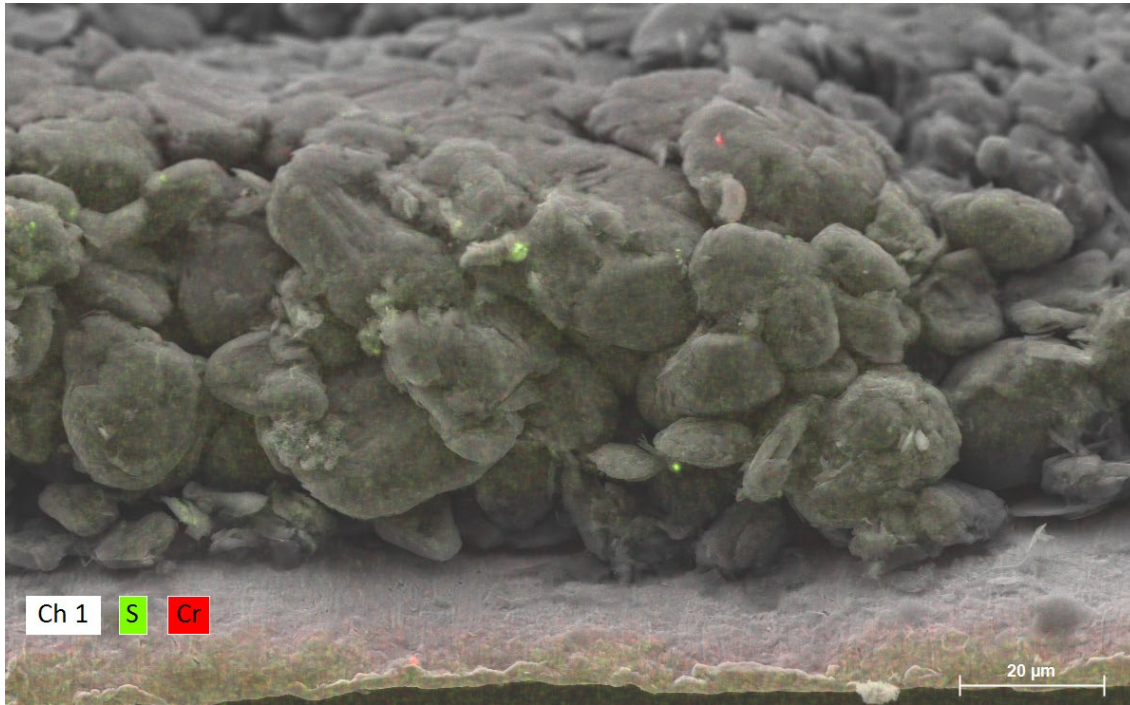


XFlash® FlatQUAD

Less noise in maps,  
Access to deeper /shadowed areas



# ANODE cross section – XFlash® 760 vs FlatQUAD: Finding “hiding elements”: S, Cr



XFlash® 760

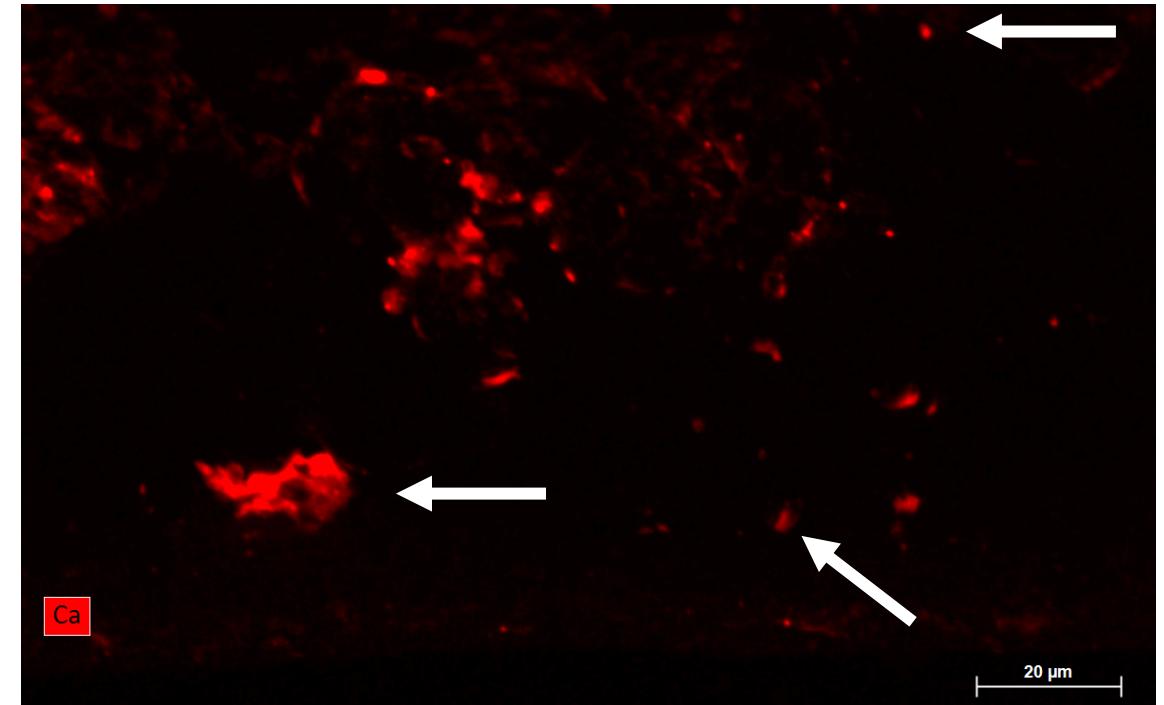
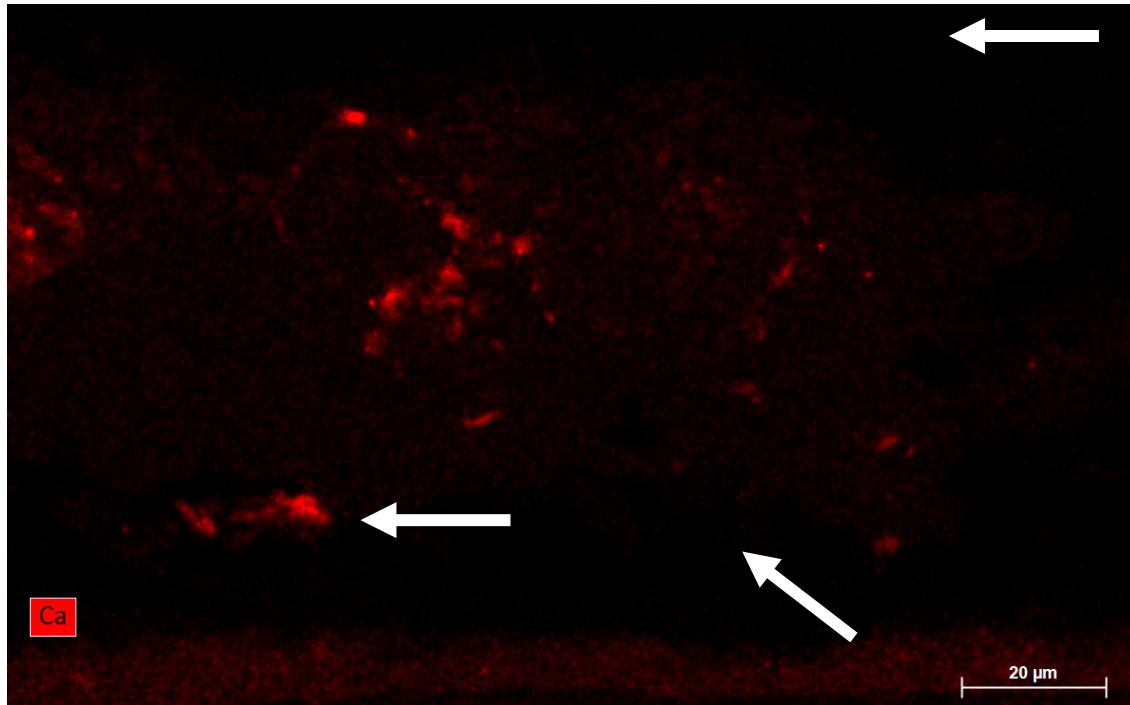
Noisier maps,  
Shadowed areas



XFlash® FlatQUAD

Less noise in maps,  
Access to deeper /shadowed areas

# ANODE cross section – XFlash® 760 vs FlatQUAD: Finding “hiding elements”: Ca



XFlash® 760

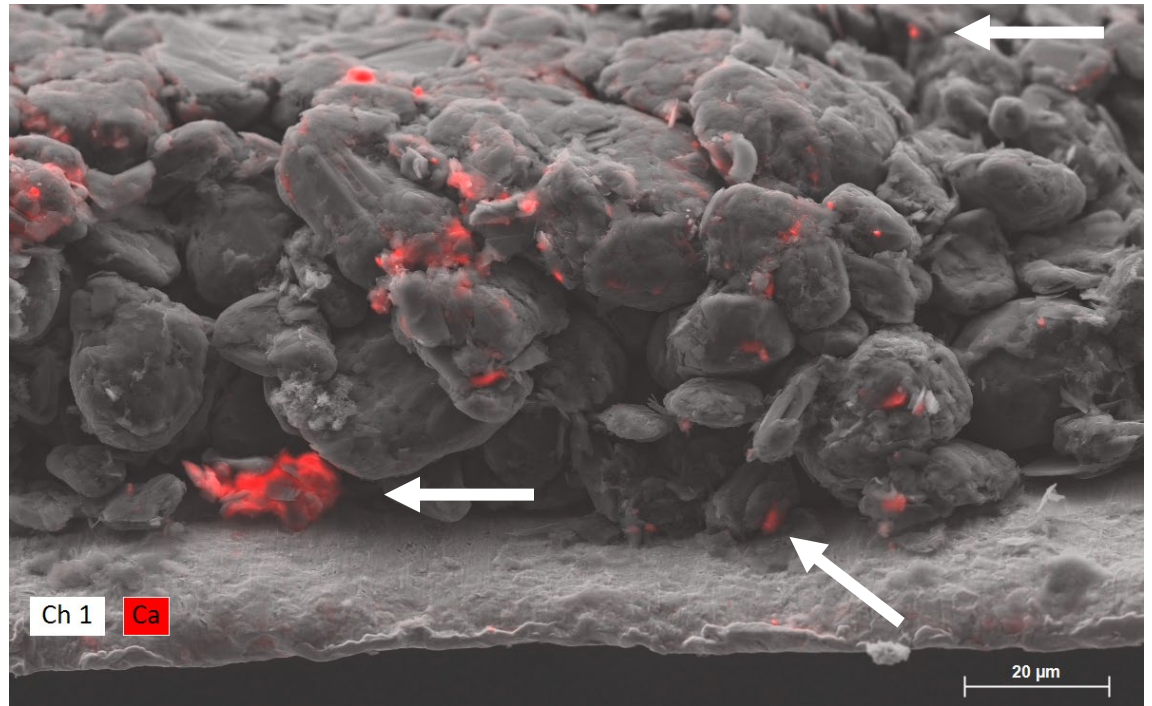
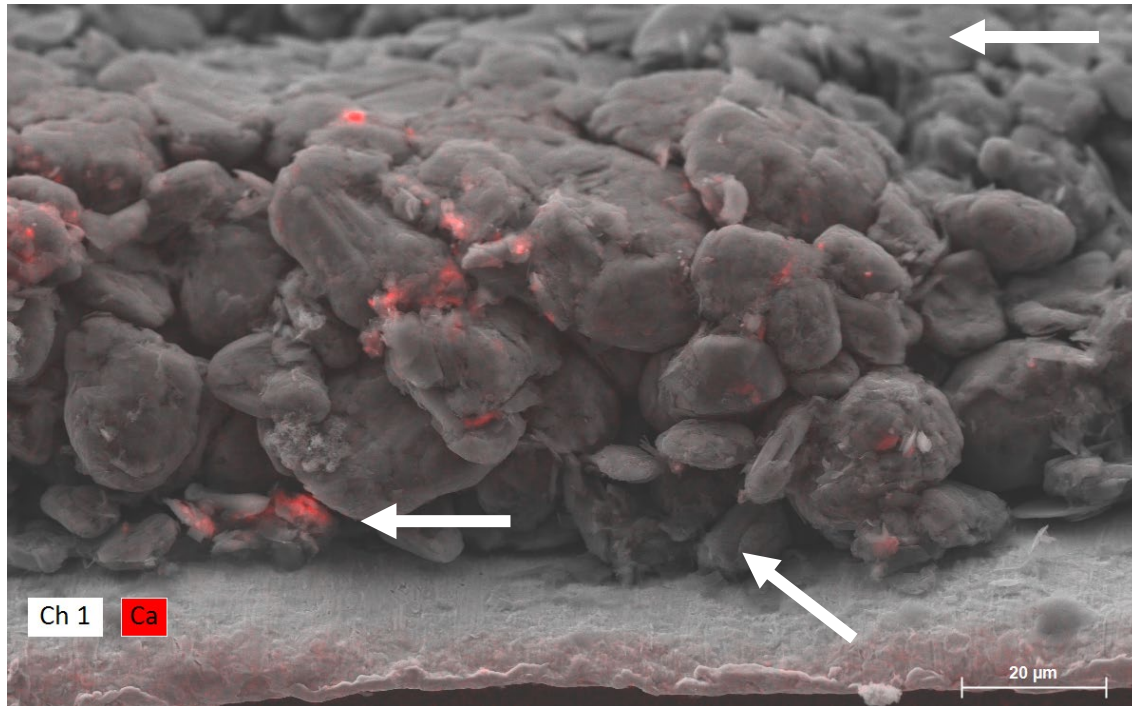
Noisier maps,  
Shadowed areas



XFlash® FlatQUAD

Less noise in maps,  
Access to deeper /shadowed areas

# ANODE cross section – XFlash® 760 vs FlatQUAD: Finding “hiding elements”: Ca



XFlash® 760

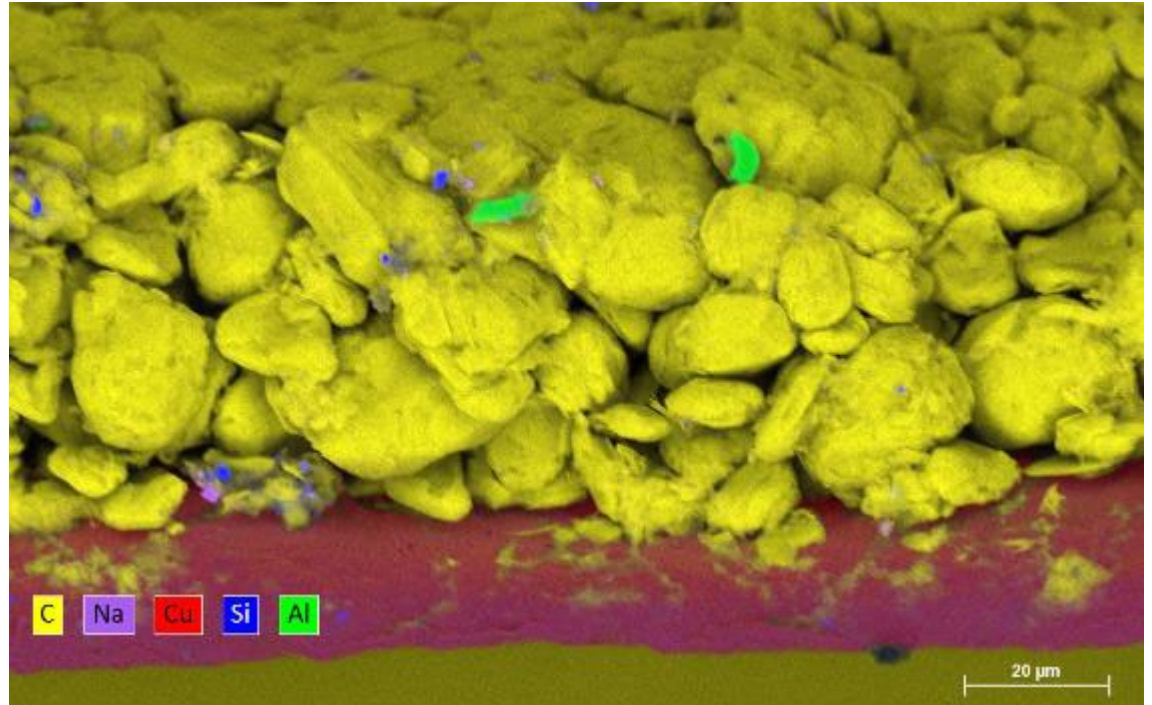
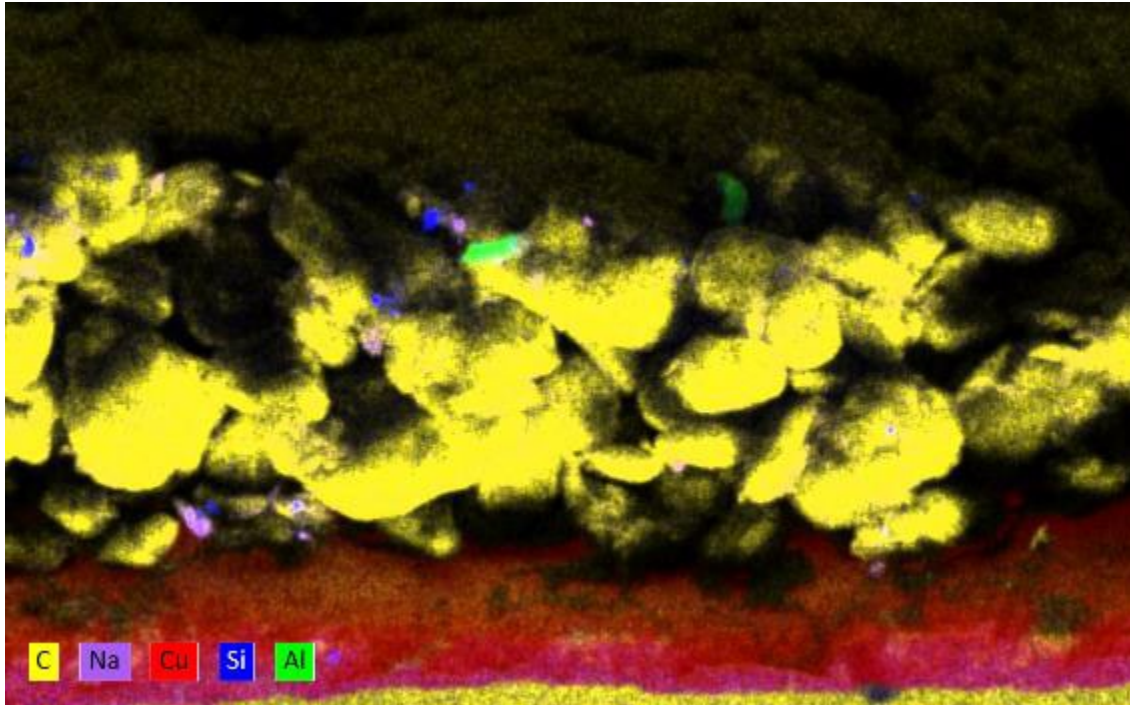
Noisier maps,  
Shadowed areas



XFlash® FlatQUAD

Less noise in maps,  
Access to deeper /shadowed areas

# ANODE cross section – XFlash® 760 vs FlatQUAD



XFlash® 760

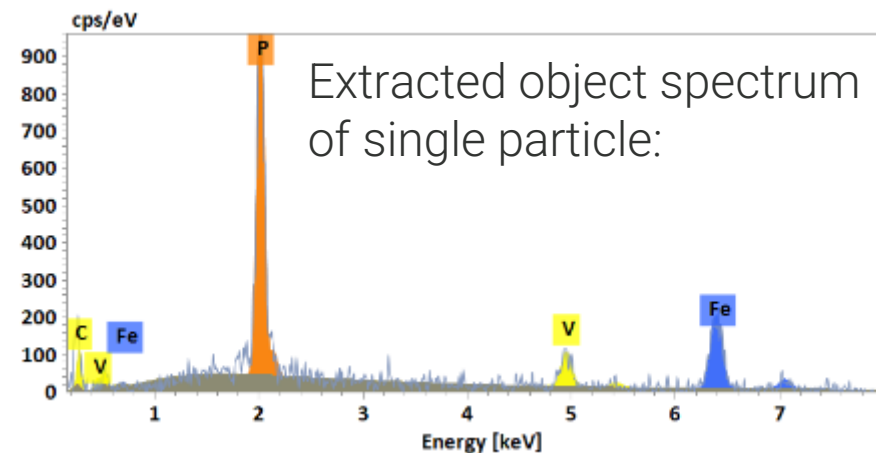
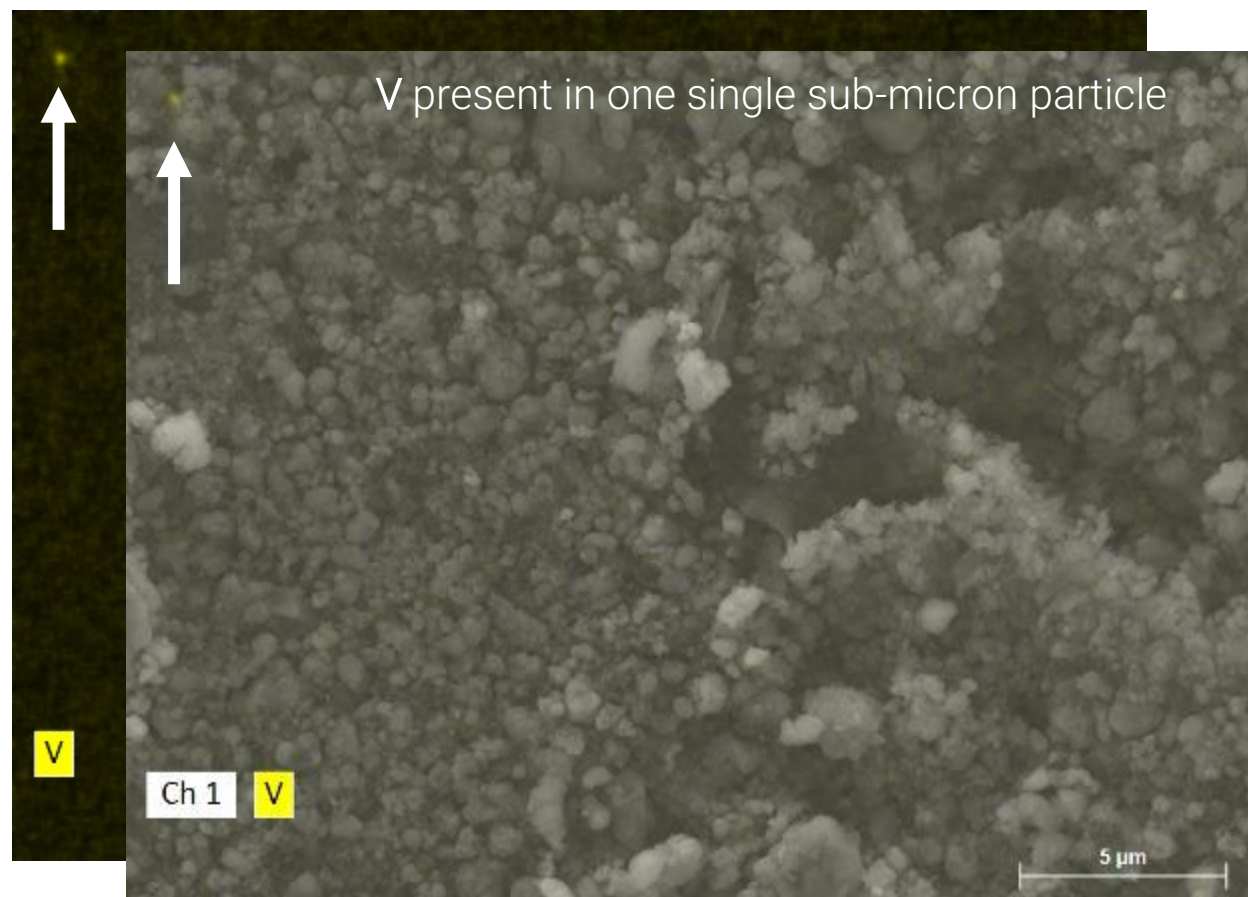
Noisier maps,  
Shadowed areas



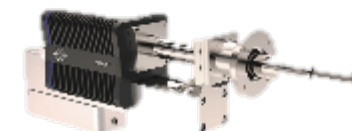
XFlash® FlatQUAD

Less noise in maps,  
Access to deeper /shadowed areas

# CATHODE - Identify and locate contaminants in very low concentration



Element	At. No.	Line series	Mass Norm. [%]	Atom [%]	abs. error [mass%] (3 σ)
C	6	K	6,02	19,63	2,40
P	15	K	24,35	30,79	6,66
V	23	K	11,43	8,79	4,78
Fe	26	K	58,19	40,80	25,64
			100,00	100,00	



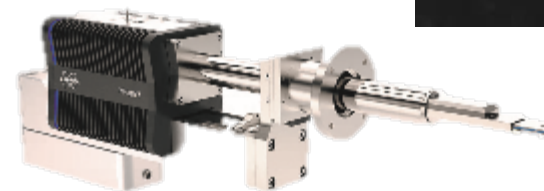
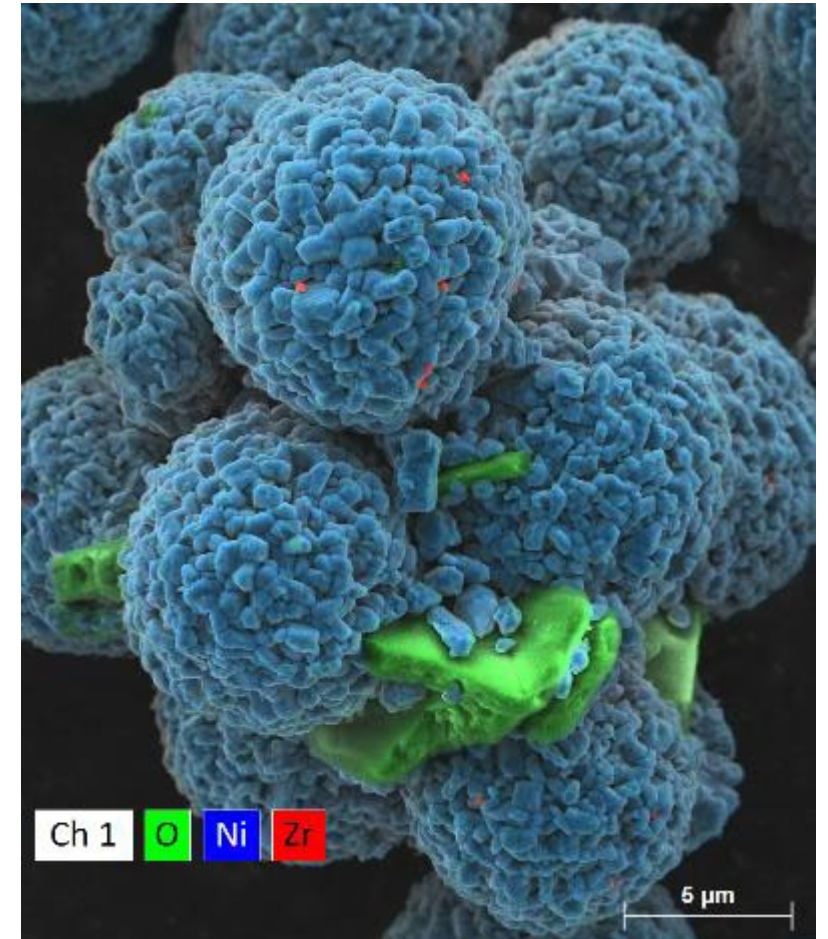
Area coverage= 0.01%

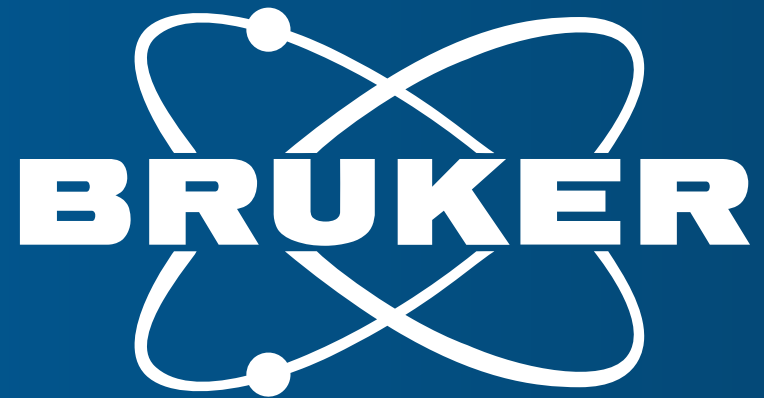
Local concentration of V: 11% -> 11 ppm V detected within 3 minutes of measurement time!

XFlash® FlatQUAD

## Summary

- XFlash® FlatQUAD: High sensitivity, high speed at low probe currents
- Faster chemical analysis of battery materials at high resolution / large area analysis
- Battery materials highly topographic: Better view of topography, hidden elements/contaminants visible
- 4 segment, side entry EDS detector, detection from Boron, ideal for battery applications





Innovation with Integrity

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[www.bruker.com/bna](http://www.bruker.com/bna)